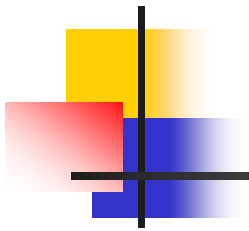


微小世界是如何運作的

---微機電系統

國立成功大學
材料科學及工程學系
特聘教授
張炎輝



- Introduction
- Surface micromachining
- Bulk micromachining
- Applications
- Conclusion

Micro and Nano technologies - status

■ Micro technologies

- 1/1,000,000 of a meter
- Devices dimensions today in the Microelectronics industry $\sim 0.065 \mu\text{m}$
- The dimensions will reach $0.035 \mu\text{m}$ in 2010
- ~ 9000 million devices on a chip

• Nano technologies

- 1/1,000,000,000 of a meter
- 1000 Billion devices on a chip
- Atomic scale devices
- Not in production..... yet

Microsystem Technology

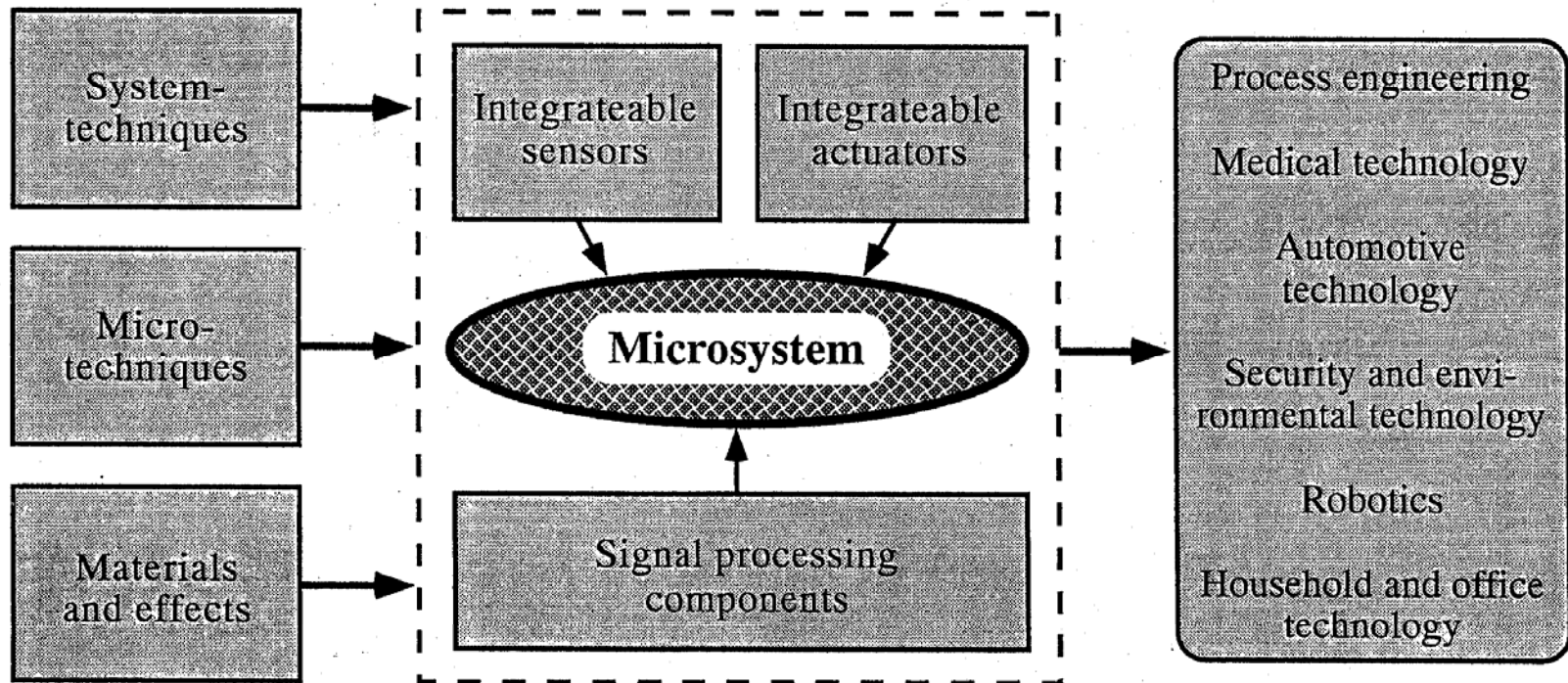
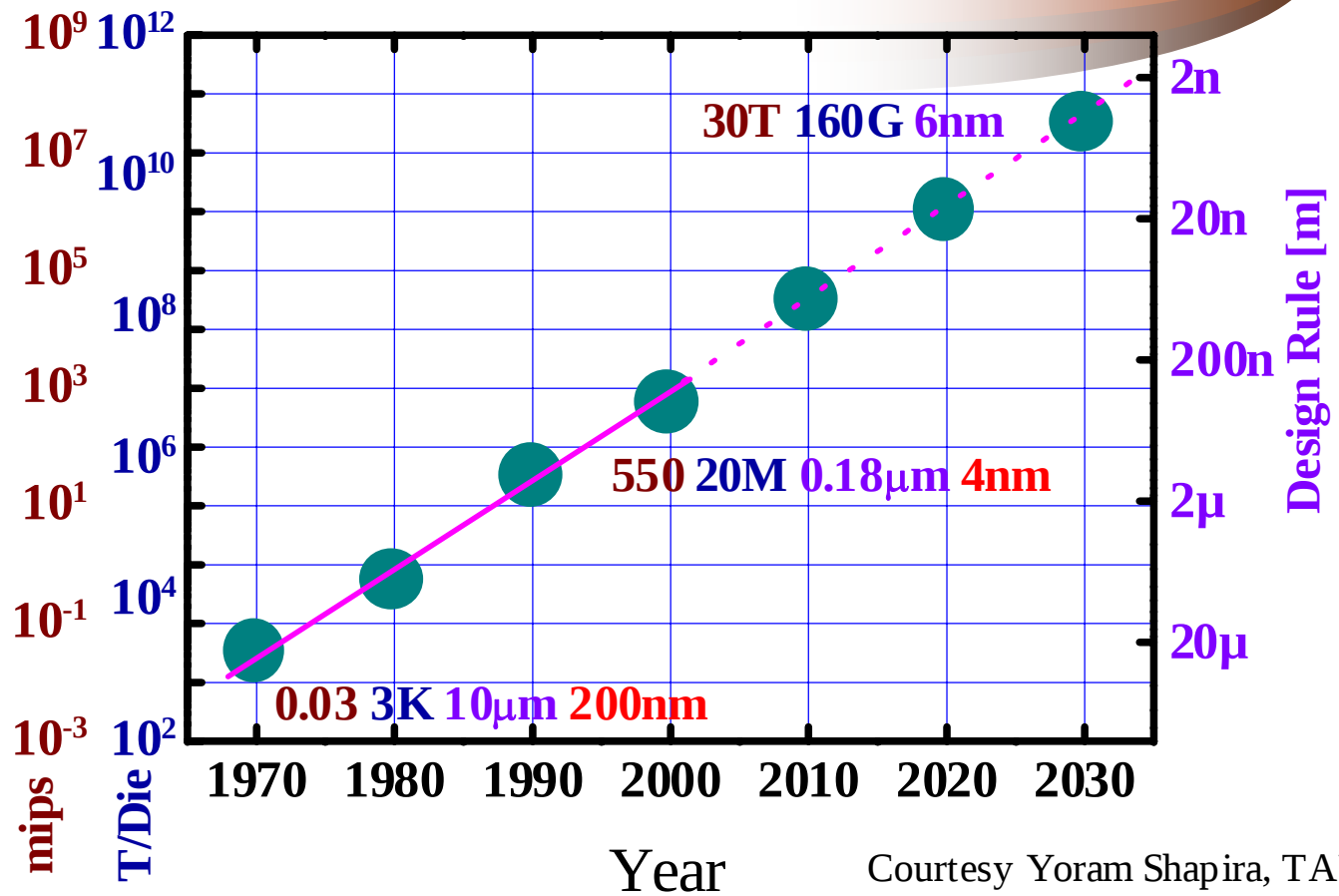


Fig. 1.1: Overview of the MST



Materials Characterization



Structure of microchips

Interconnect network - 6-7 layers of metallization

Active device layer (1-2 μm)

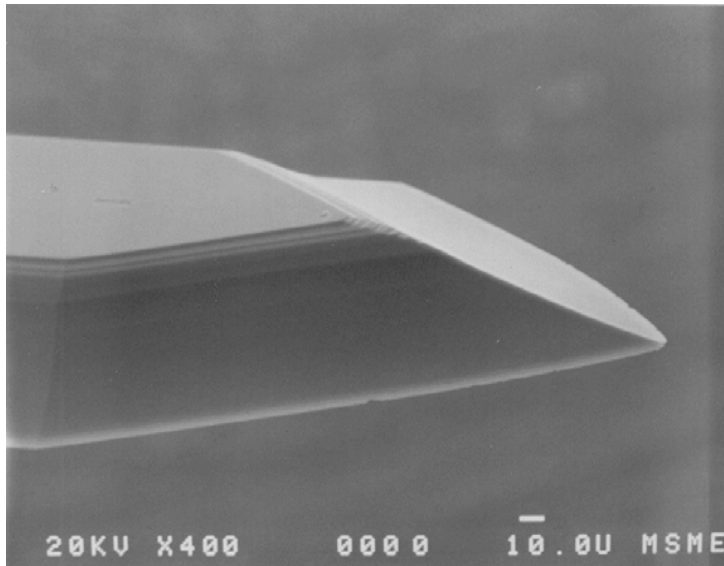
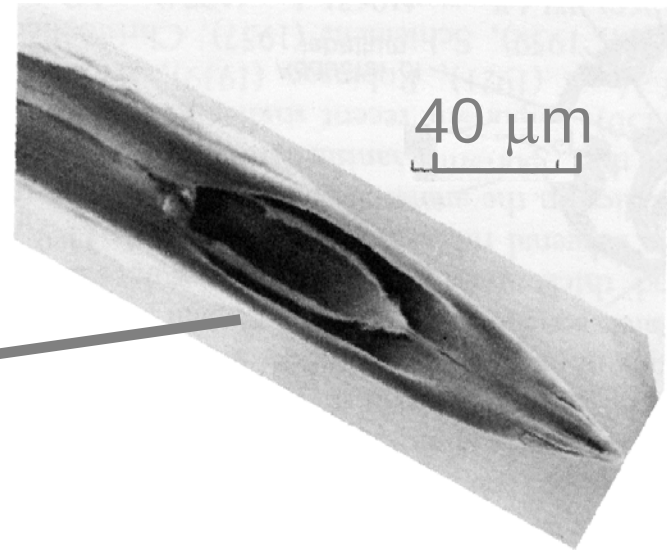
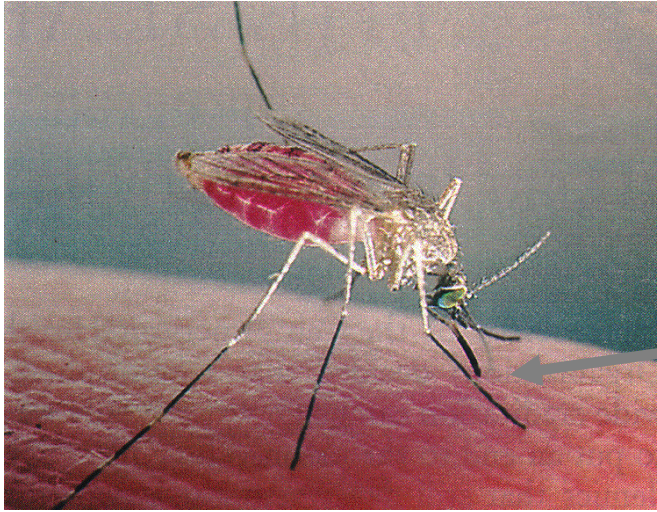
Silicon substrate (600-800 μm)

Multi-level metallization

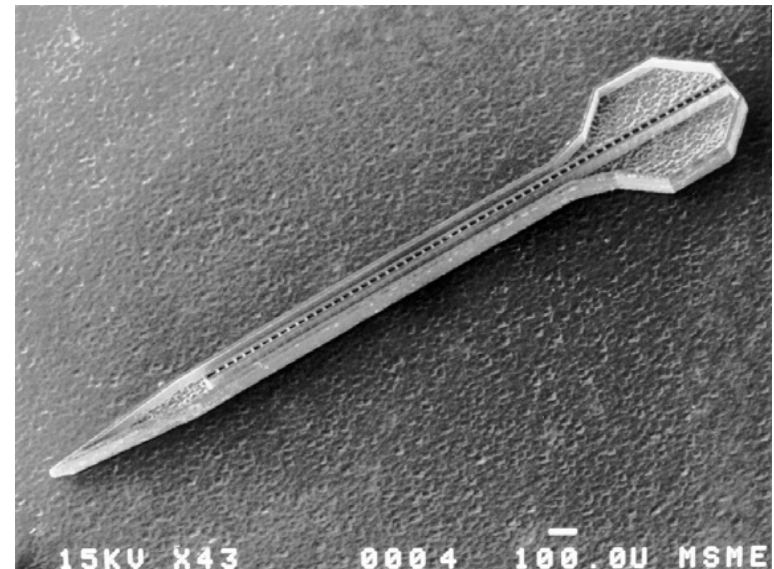


What can we put on a silicon chip ?

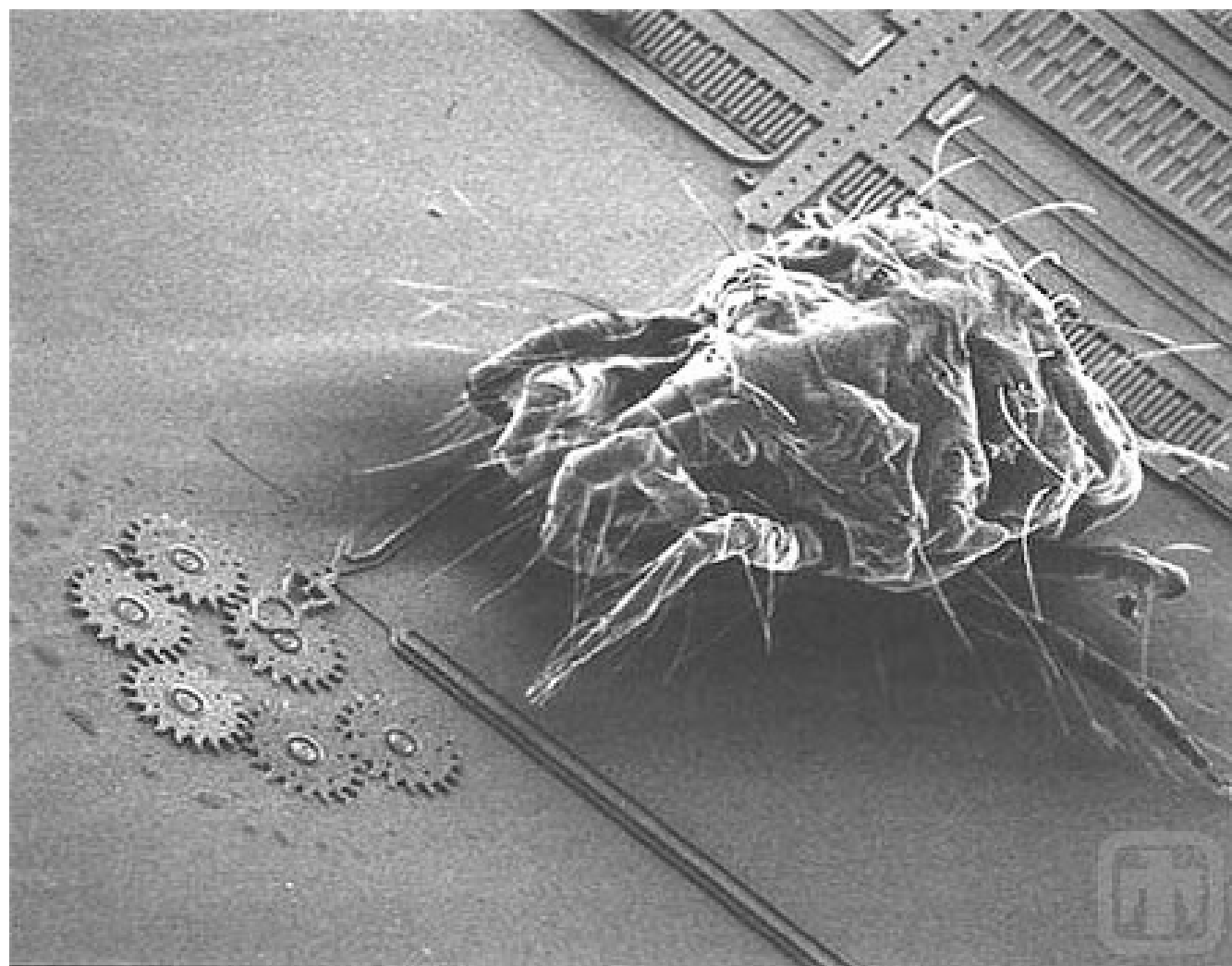
- MEMS - Micro Electro Mechanical Systems
- MEOMS - Micro Electro Optical Mechanical Systems
- Micro-biological systems
- Micro-Chemistry, and
- Microelectronics.....

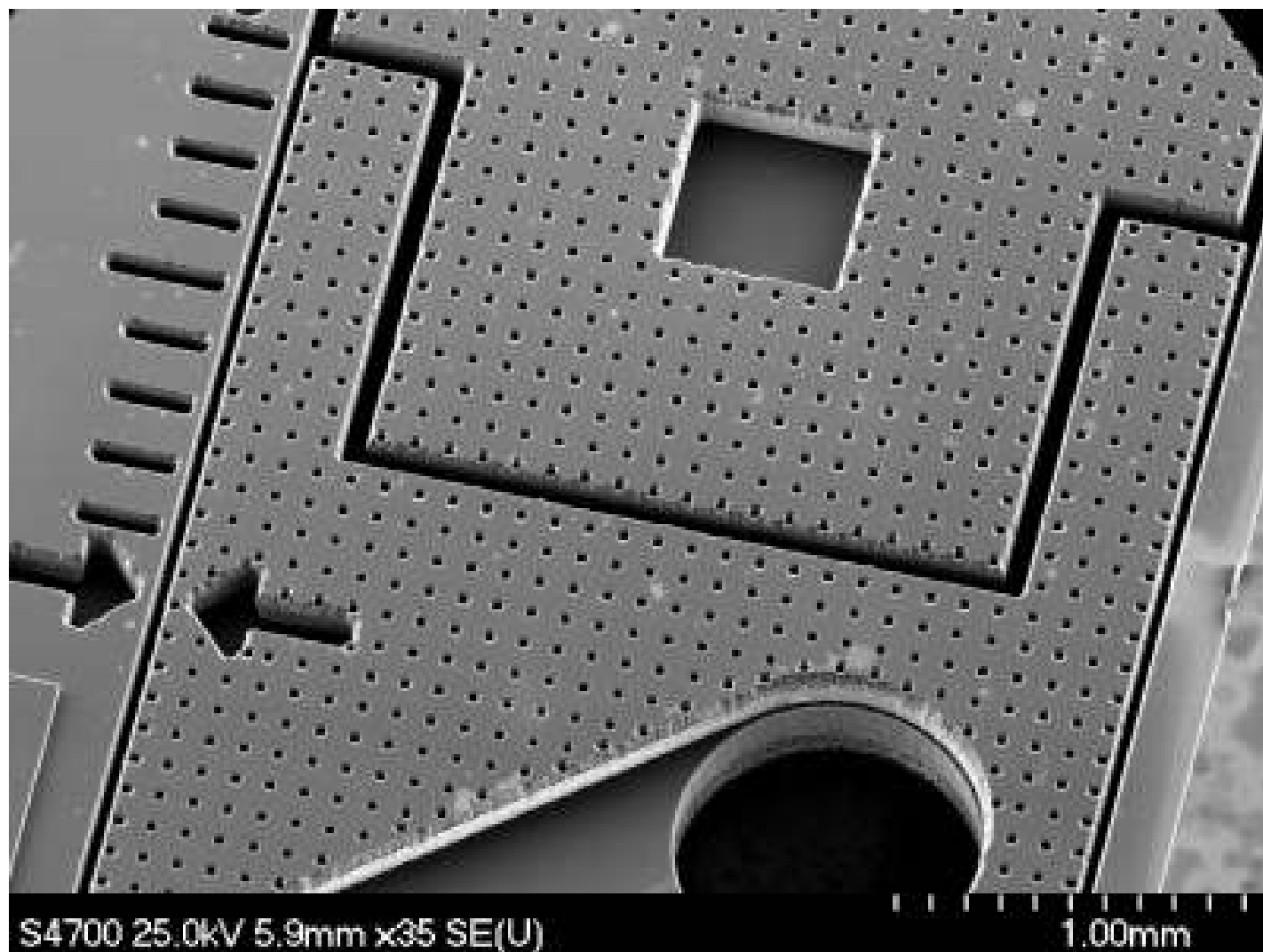


Lancet width = 170 μm



Needle width = 150 μm





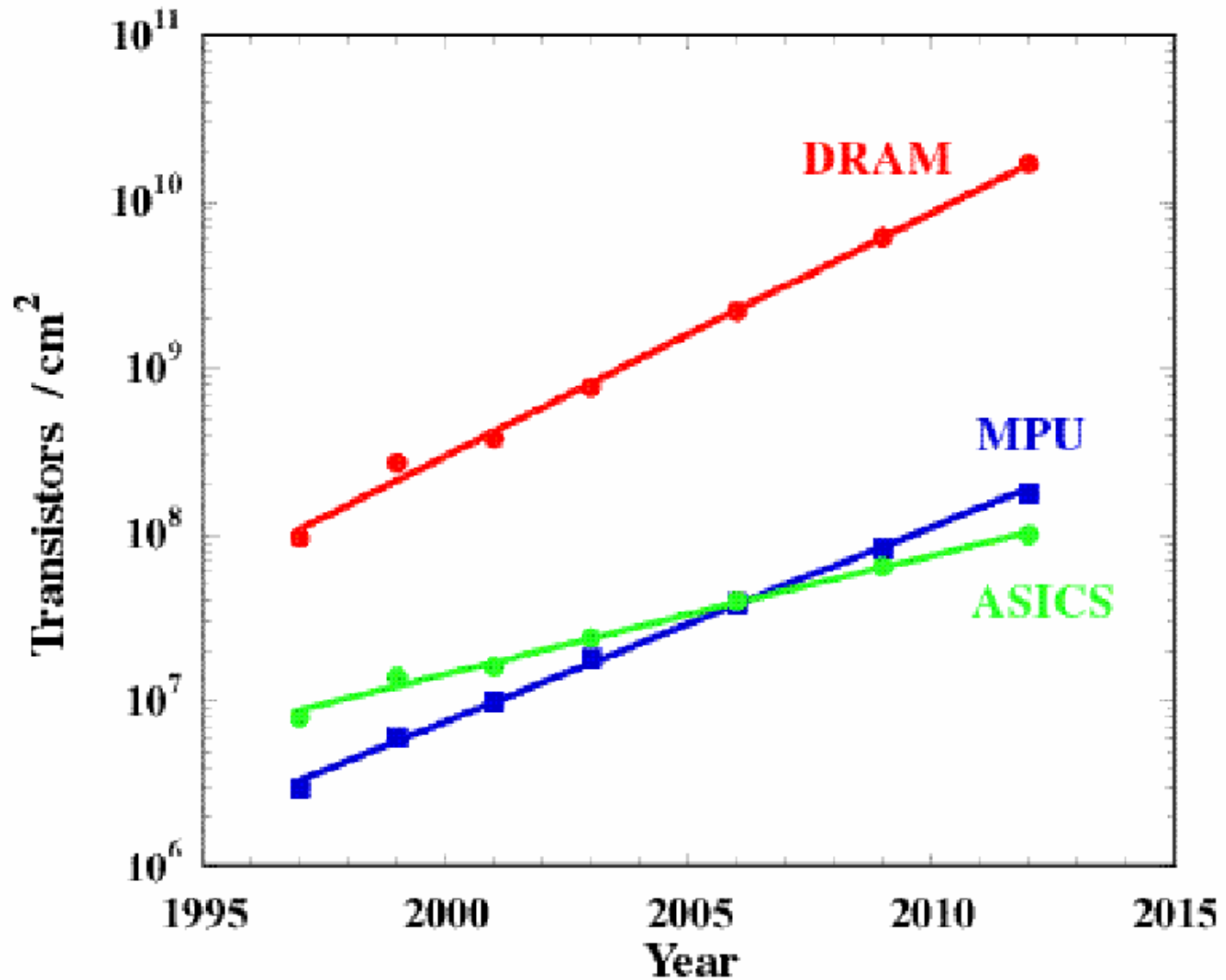
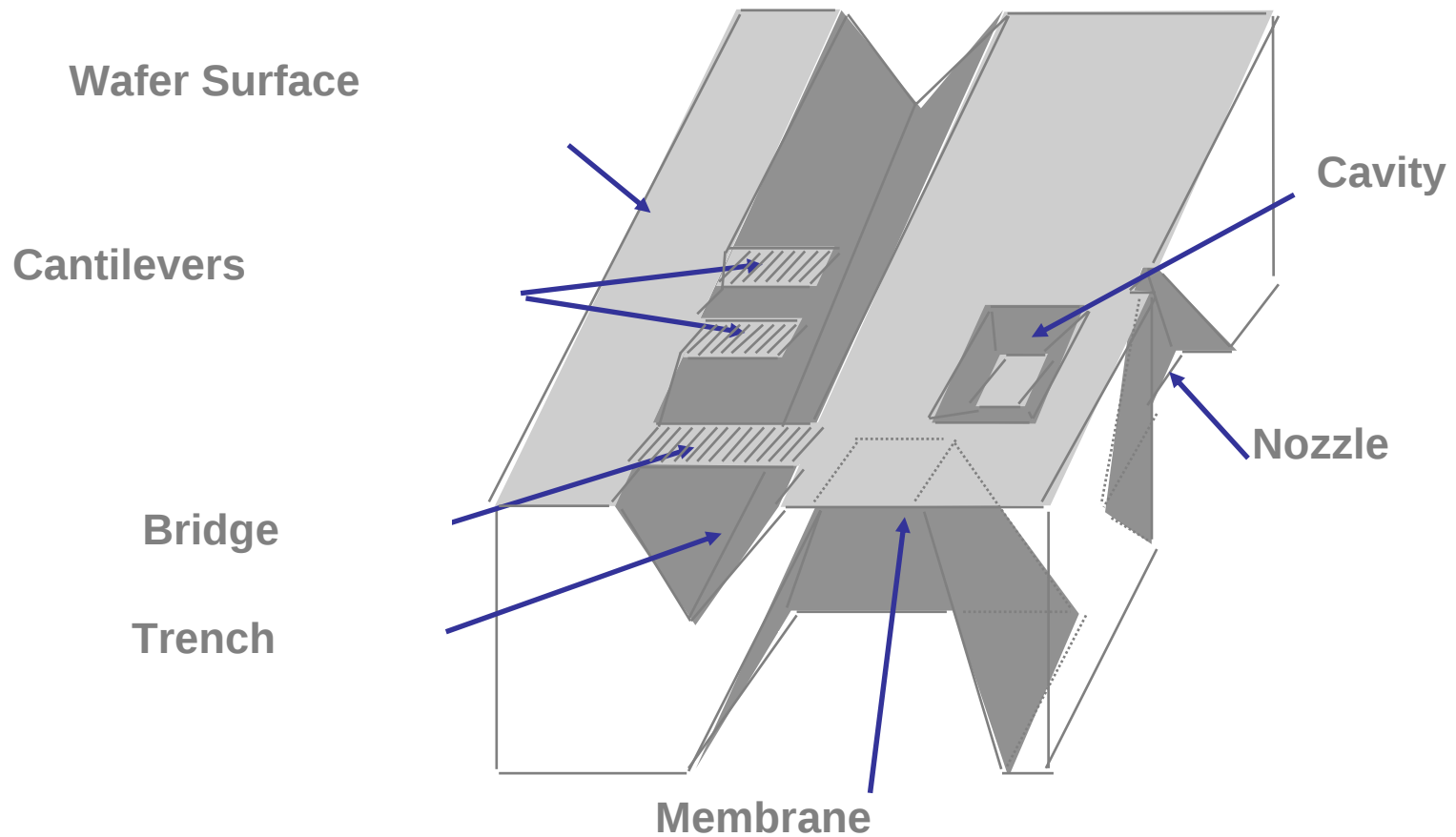


Figure 1.2:- The number of transistors per cm^2 plotted against the year of first manufacture.

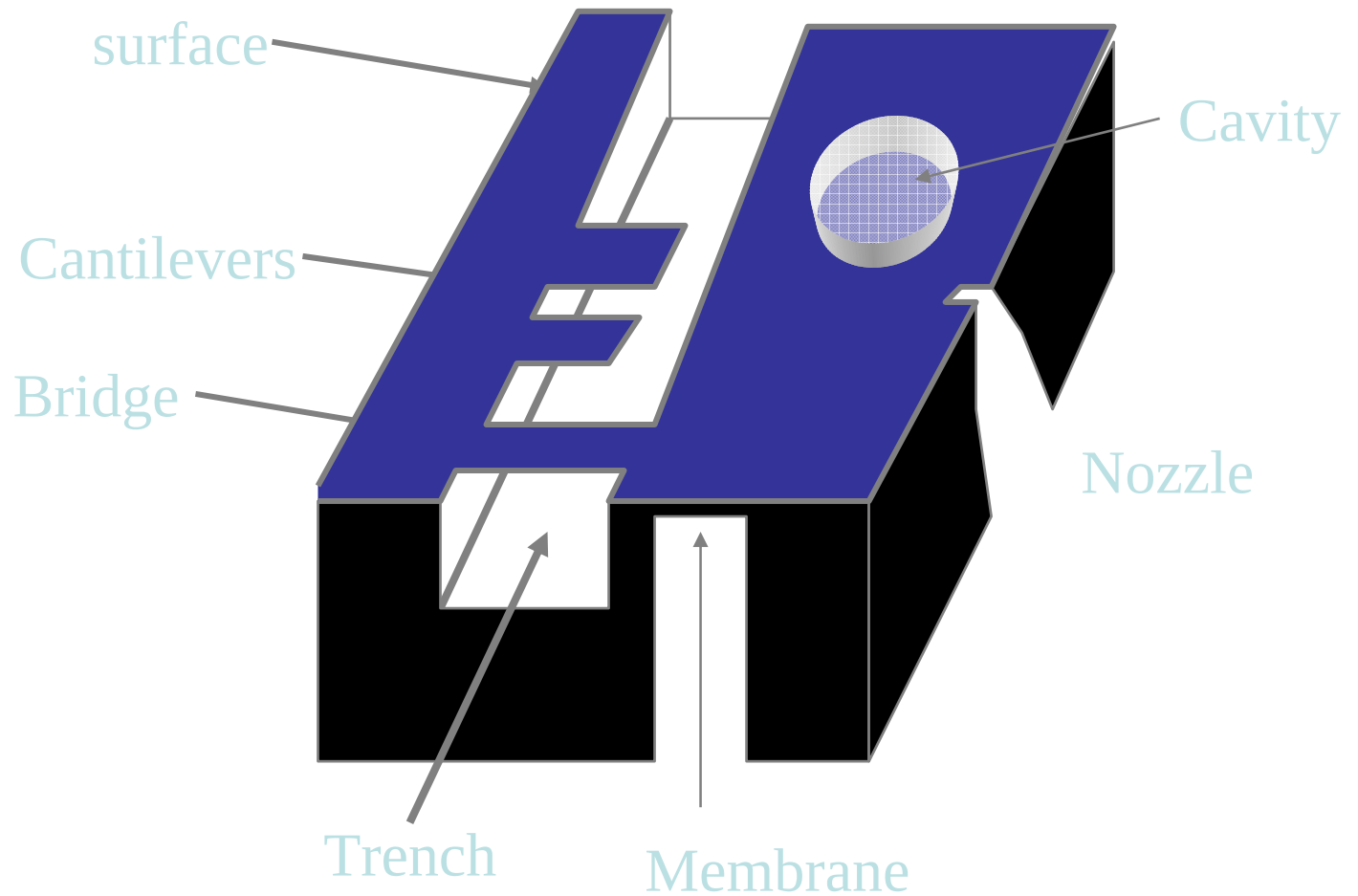
Fabrication

- Bulk micro-machining
 - etch into the substrate
- Surface micro-machining
 - build up layers above the substrate and etch
- LIGA
 - deep structures

Single crystal **Bulk** Micromachining

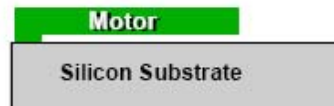
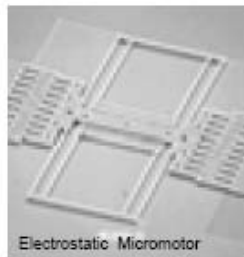


Non crystal **Bulk** Micromachining



The More Mechanical Levels The More Sophisticated The Device

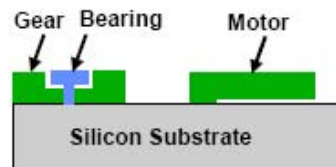
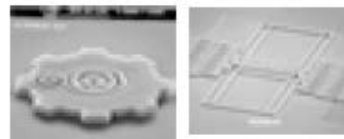
2-Level



■ Polysilicon Level #1

Sensors

3-Level

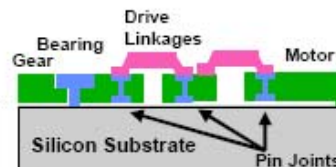
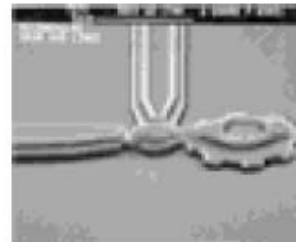


■ Polysilicon Level #1

■ Polysilicon Level #2

Advanced Sensors
Simple Actuators

4-Level



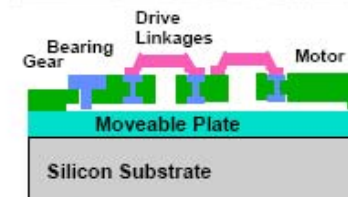
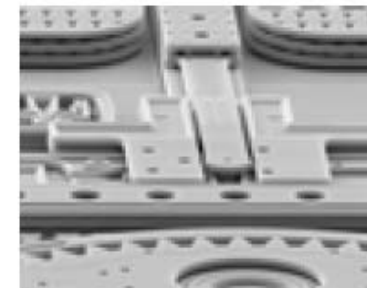
■ Polysilicon Level #1

■ Polysilicon Level #2

■ Polysilicon Level #3

Advanced Actuators

5-Level



■ Polysilicon Level #1

■ Polysilicon Level #2

■ Polysilicon Level #3

■ Polysilicon Level #4

Complex Systems

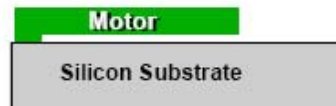
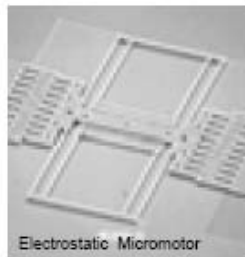
Surface micromachining

- Specifically - MUMPS (Multi-User MEMS Processes)¹
 - MUMPS has been called “MOSIS for MEMS”
 - Three poly layer process derived from Berkeley Sensors and Actuators Center
 - Seven total material layers
 - N mask steps

¹ Figures are plagiarized from MUMPS , MCNC.

The More Mechanical Levels The More Sophisticated The Device

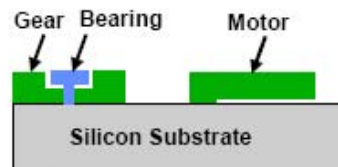
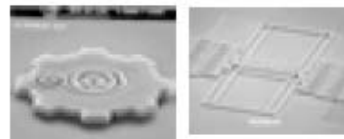
2-Level



■ Polysilicon Level #1

Sensors

3-Level

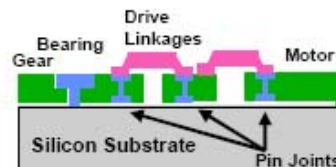
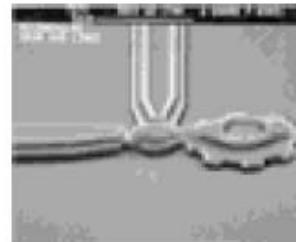


■ Polysilicon Level #1

■ Polysilicon Level #2

**Advanced Sensors
Simple Actuators**

4-Level



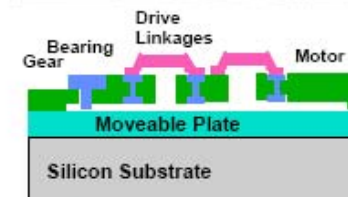
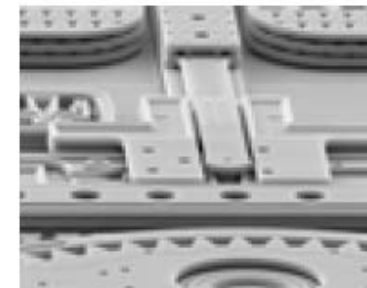
■ Polysilicon Level #1

■ Polysilicon Level #2

■ Polysilicon Level #3

Advanced Actuators

5-Level



■ Polysilicon Level #1

■ Polysilicon Level #2

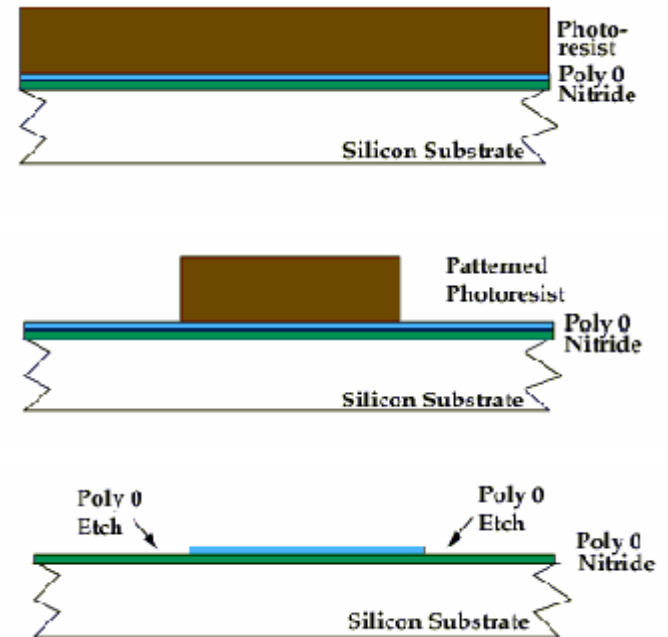
■ Polysilicon Level #3

■ Polysilicon Level #4

Complex Systems

Patterning Poly 0

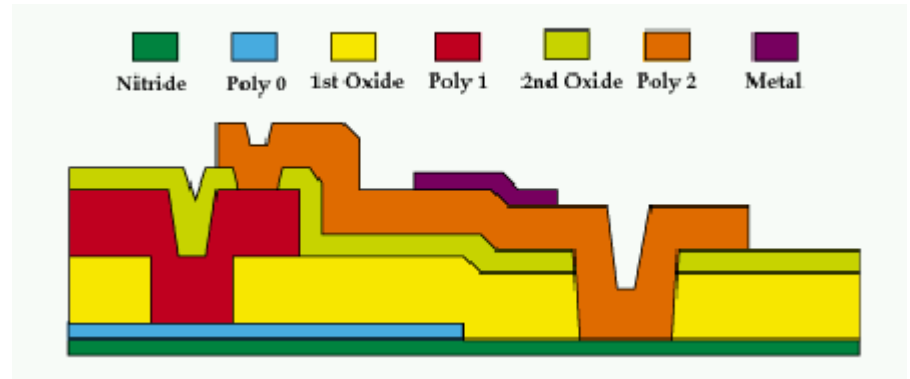
- Initial layers:
 - substrate/nitride/poly0/resist
- Expose resist
- Dissolve exposed resist
- Etch poly0
- Wash remaining resist



Poly0 is an electrical layer.

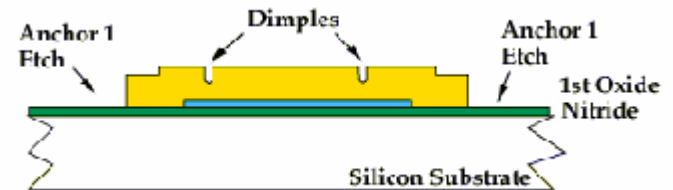
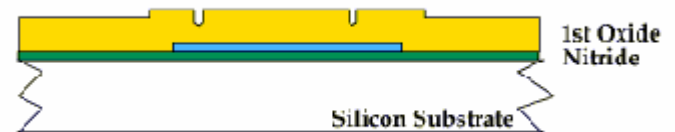
Processing Layers

- 7 material layers/
 - isolation
 - conductor (poly)
 - 1st sacrificial (oxide)
 - 1st structural (poly)
 - 2nd sacrificial (oxide)
 - 2nd structural (poly)
 - metal



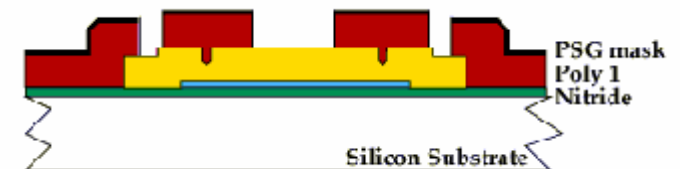
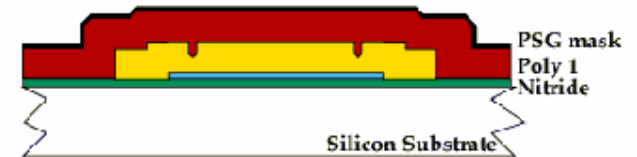
First Sacrificial (oxide) Layer

- This layer will eventually be dissolved. Its purpose is to support the structural layer (poly1) above it.
- Note: all layers are conformal
- Two timed etches - short for dimples, longer for anchor



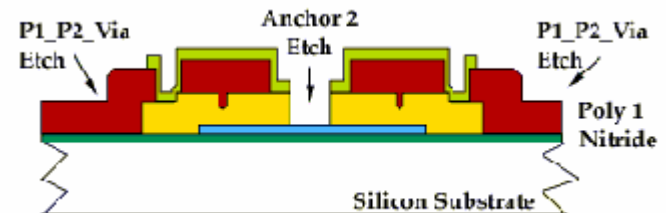
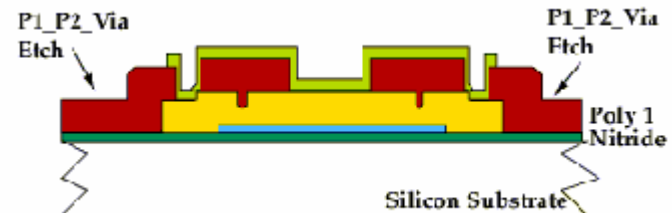
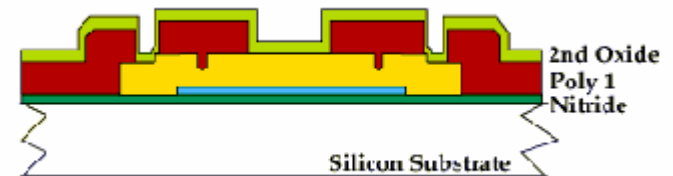
First structural (poly1) layer

- Deposit $2\mu\text{m}$ of polysilicon
- Coat with resist, expose
- Etch with RIE (reactive ion etch)



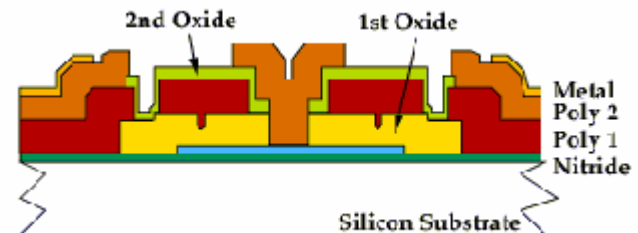
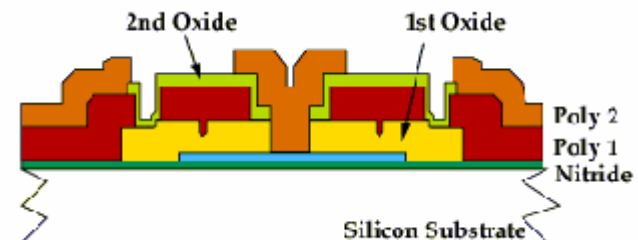
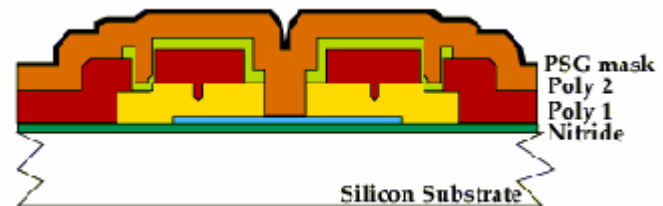
2nd sacrificial (oxide) layer

- Deposit 0.75 μm oxide
- Two etch steps - first contacts poly1, second contacts substrate



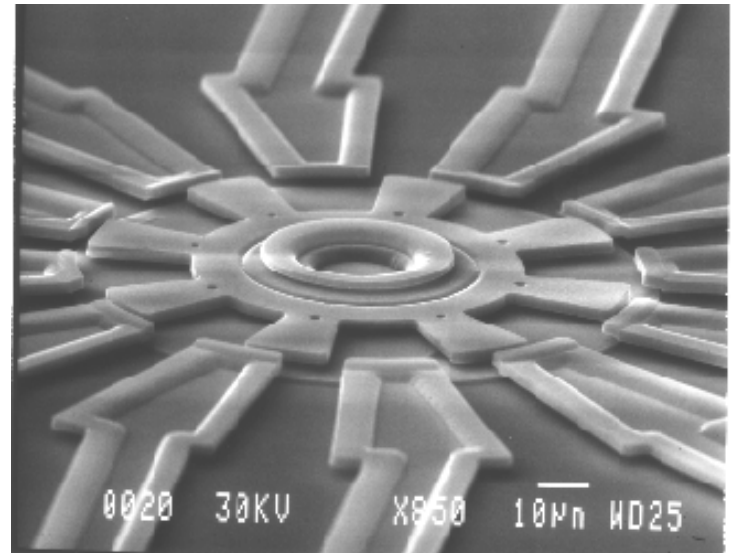
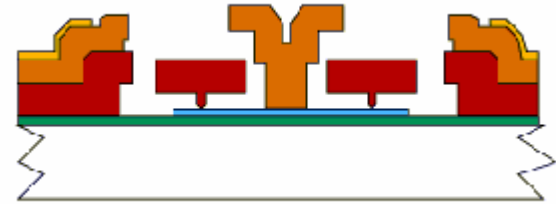
2nd structural (poly2) layer + metal

- Deposit second poly layer
- Apply resist and etch (RIE)
- Apply resist and etch
- Deposit metal, gold in MUMPS



Released mechanism

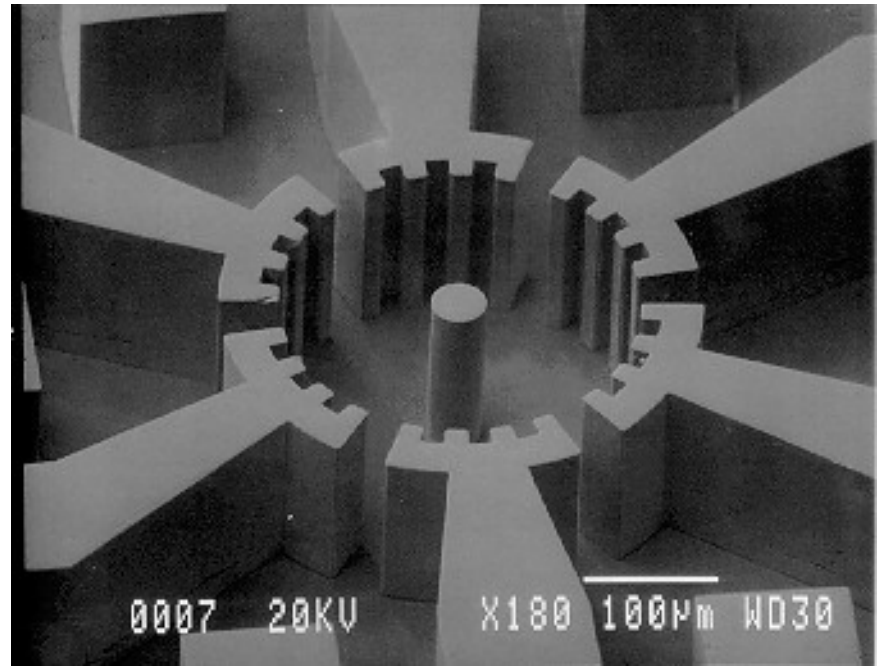
- Rinse in solvent to remove resist and overlying metal
- Soak 2 minutes in concentrated HF to dissolve sacrificial oxide layers



LIGA

Lithographie, Galvanoformung, Abformung

- 200 μm deep structures
- Coat with thick resist
- Pattern with Xrays
- Electroplate exposed area with Ni
- Machine to $\pm 5\mu\text{m}$
- Use titanium and Cu as sacrificial layers

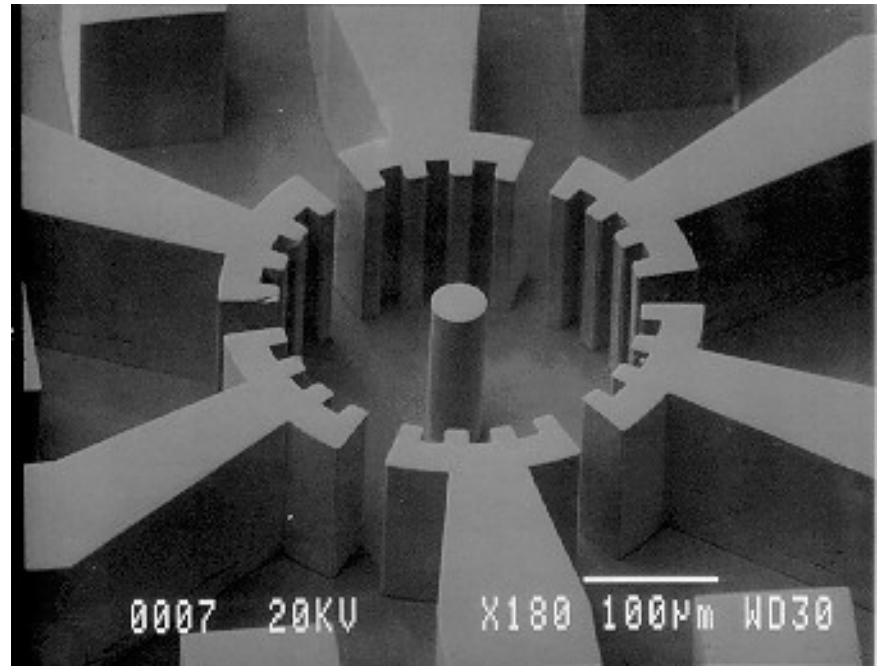


MCNC

LIGA

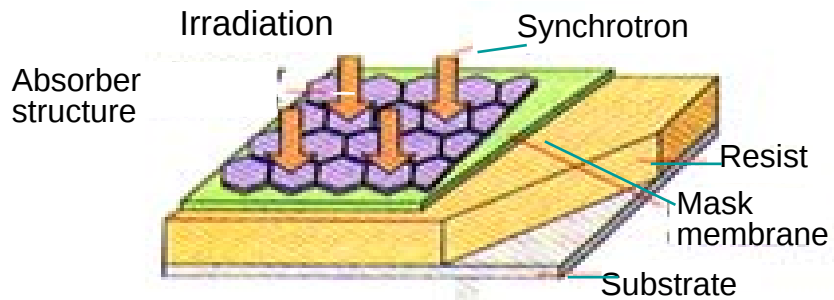
Lithographie, Galvanoformung, Abformung

- 200 μm deep structures
- Coat with thick resist
- Pattern with Xrays
- Electroplate exposed area with Ni
- Machine to $\pm 5\mu\text{m}$
- Use titanium and Cu as sacrificial layers

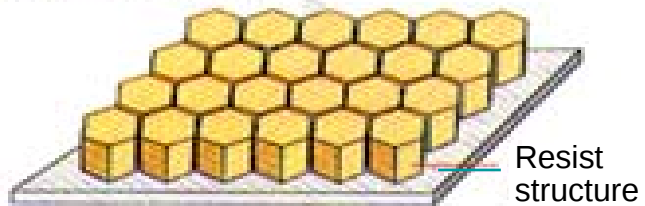


MCNC

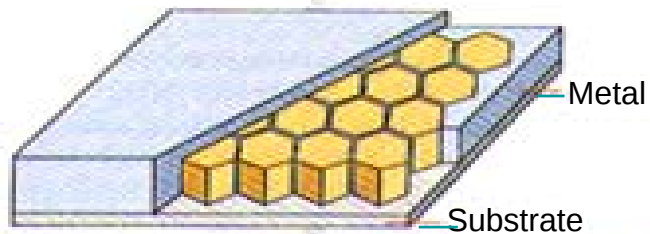
LIGA*, Deep UV



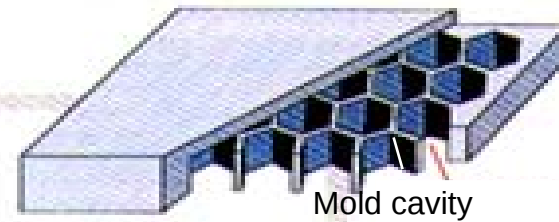
Development



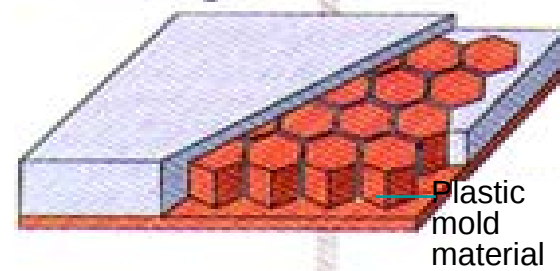
Electroforming



Mold Insert

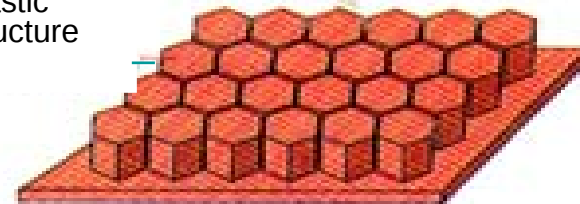


Mold Filling



Mold Separation

Plastic structure



Source: IMM (Mainz Institute for Microtechnology)

*Lithographie, Galvanoformung, Abformung

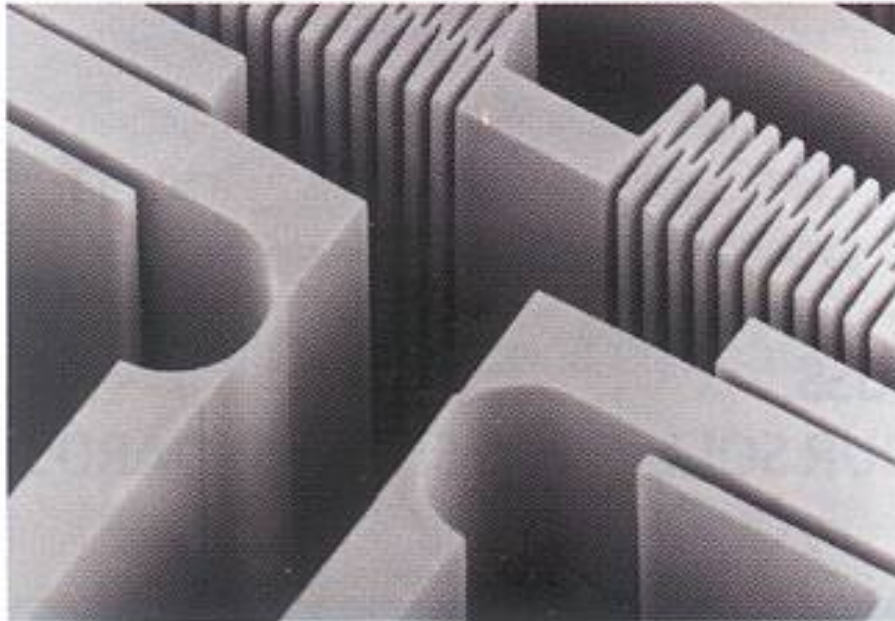


Fig. 2: PMMA mold of an electrostatic actuator manufactured by X-ray deep lithography before the electro-deposition of nickel. The height is 100 μm , the smallest lateral dimension 1 μm .

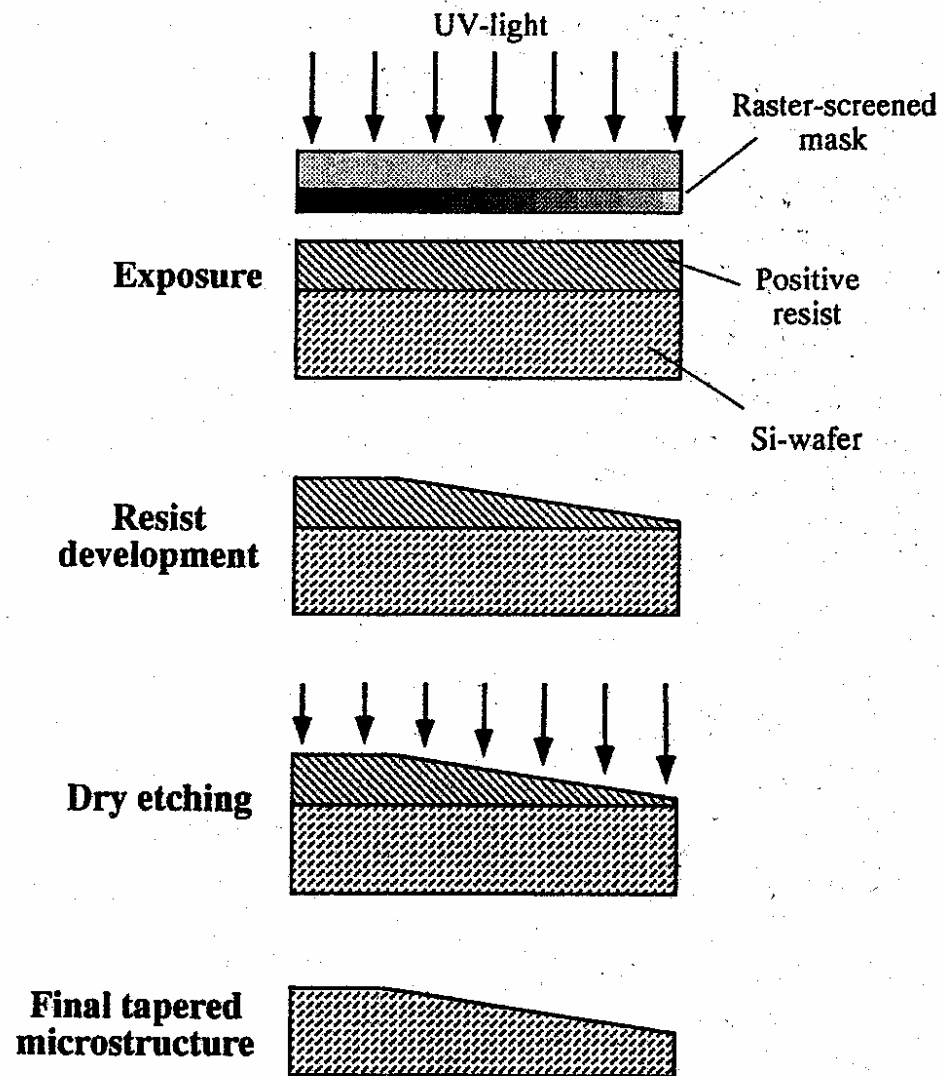


Fig. 4.4: Principle of gray-tone lithography. According to [Weng94]

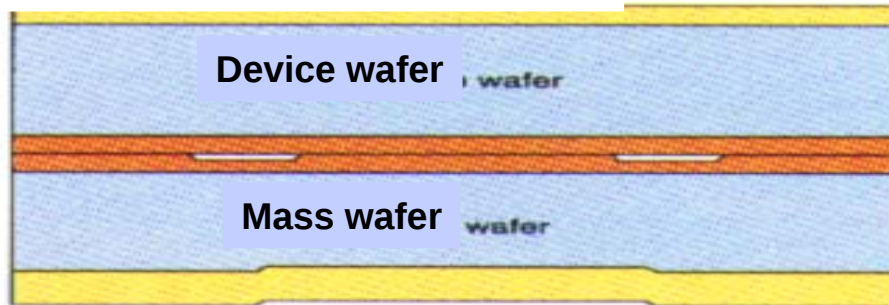


Fig. 1: parallel-produced impellers for flow sensors

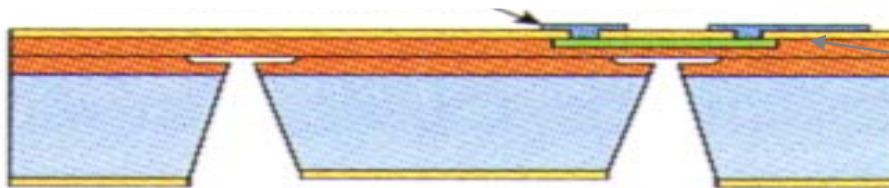
Wafer-to-Wafer Bonding



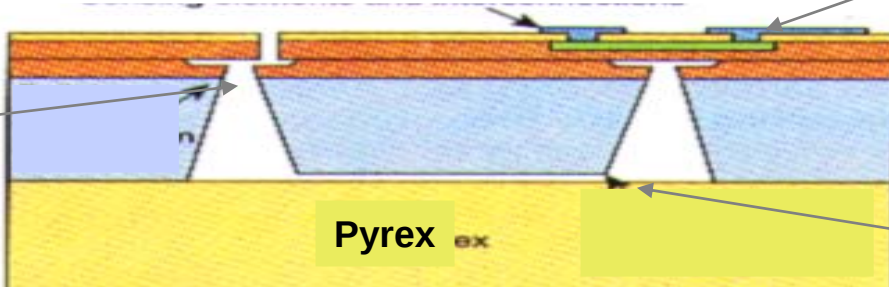
Create etch stops and gap in back



Fuse silicon



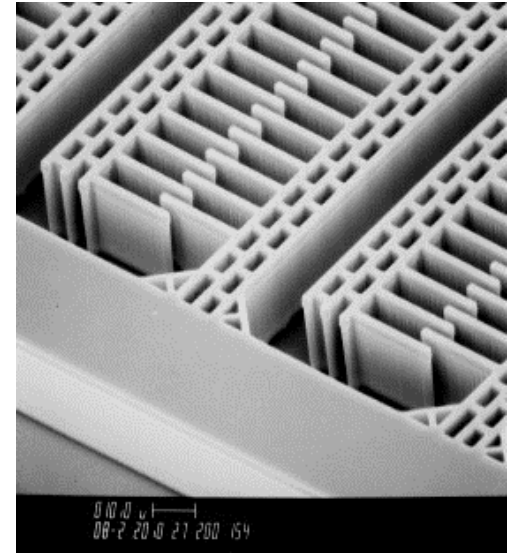
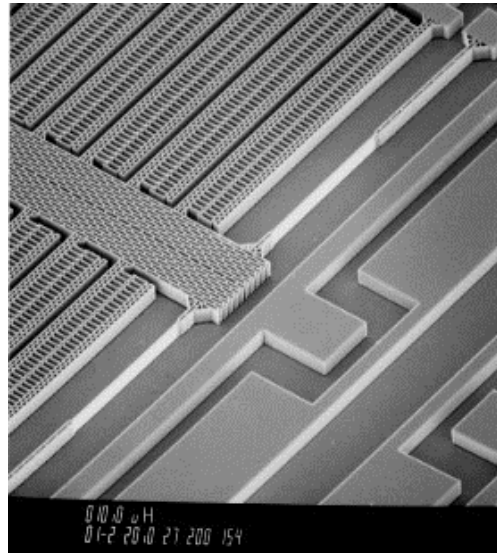
Process top and etch mass



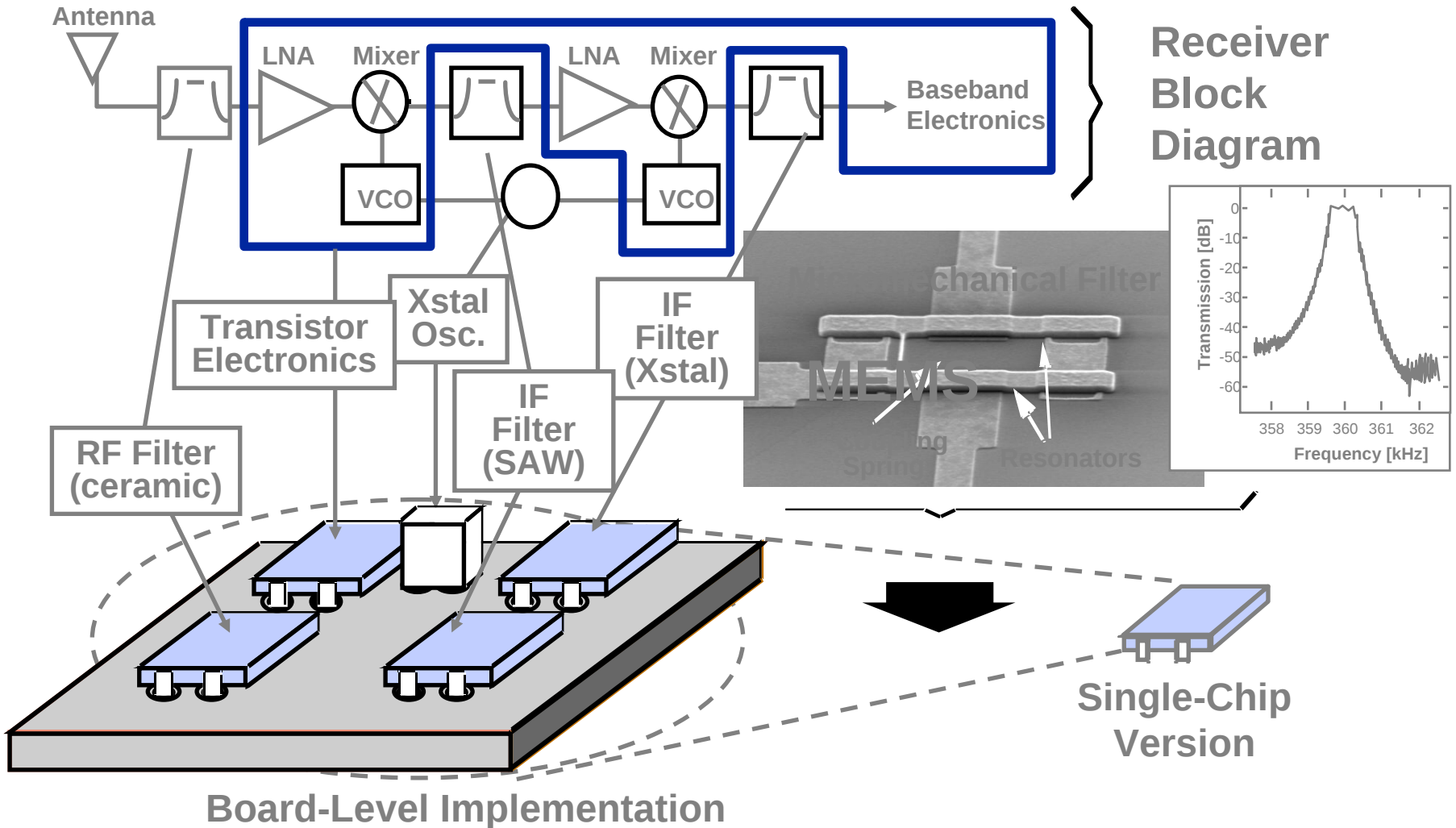
Etch beam and bond Pyrex

Highlights of the Rockwell MEMS Tunable Capacitor

- Single Crystal Silicon
- Superior Mechanical Properties
- High Aspect Ratio (20 to 1)
- Higher Linearity
- Large Tuning Ratio (> 6.5 to 1)



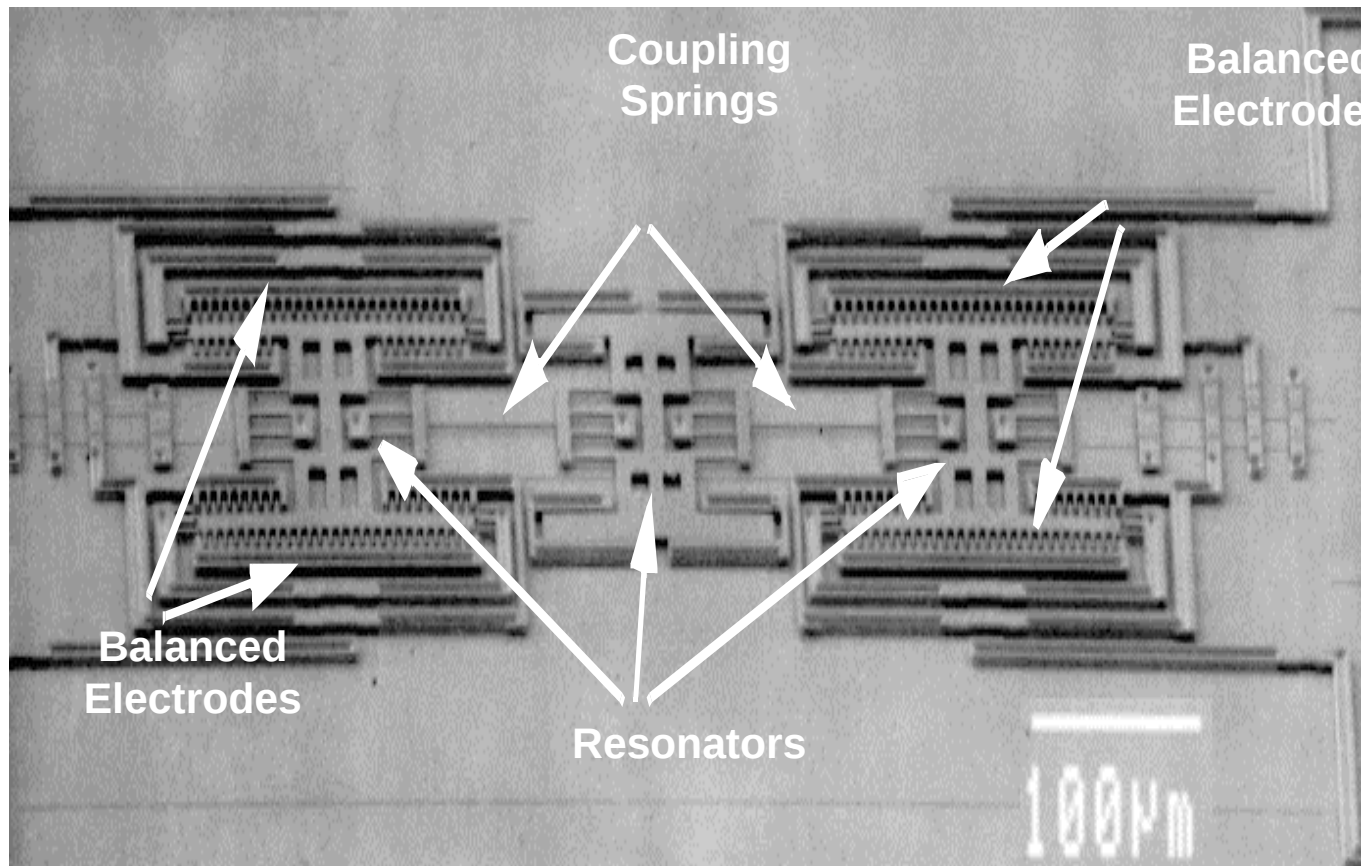
Wrist Communicator



•Off-chip high-Q mechanical components present bottlenecks to miniaturization ➡ replace them with μ mechanical versions

Sixth-Order Bandpass Filter in MEMS Technology

(200 x 700 μm)



Applications

Sensors: CO, Gyroscopes,

Actuators: Micromotors,

Optobionics: Retinal Implant, Drug

Delivery Systems,

Optical mems

Sensors

Sensors applications:

- * environmental monitoring of water and air
- * gas sensor
- * gyroscope
- * pressure sensor
- * accelerometer
- * acoustic sensor
- * SW devices sensor

Chemical analysis

Water analyzer

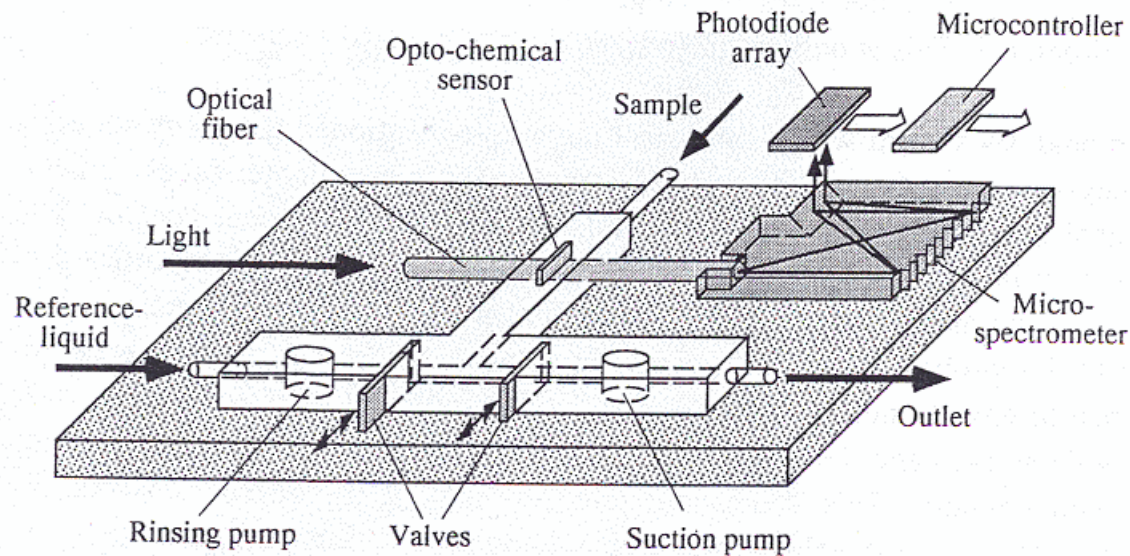
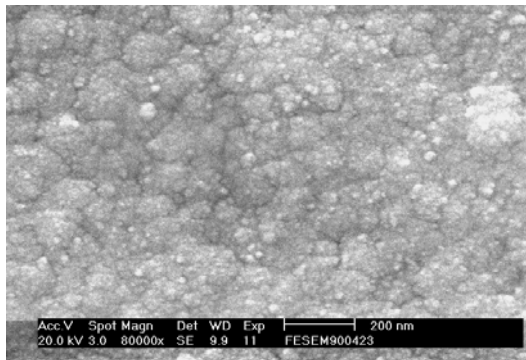


Fig. 2.9: Contaminant analyzer using an optical principle. According to [Schom93]

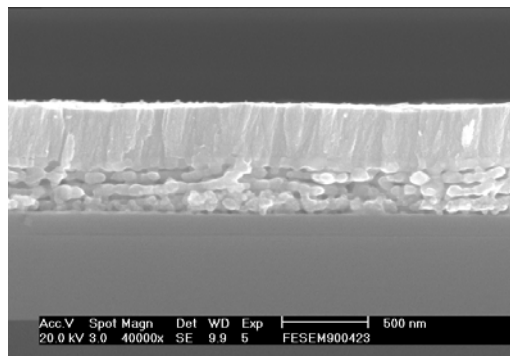
Threshold limited values of toxic gases

氣體	TLV (ppm)	氣體	TLV (ppm)
CO	50	HCN	10
NH ₃	25	HCl	5
H ₂ S	10	AsH ₃	0.05
Cl ₂	1	NO	25
SO ₂	5	NO ₂	3
C ₆ H ₆	10	CO ₂	5000
CH ₃ Br	20	O ₃	0.1
CH ₂ CH ₂ O	50	C ₂ H ₅ OH	1000

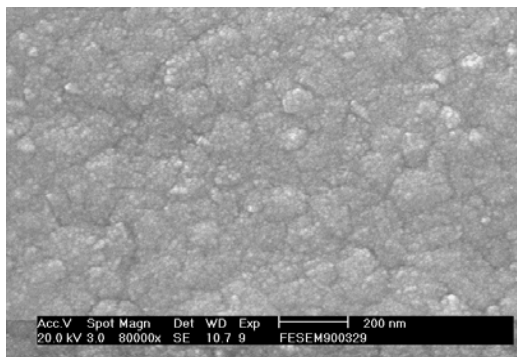
a



b



c



d

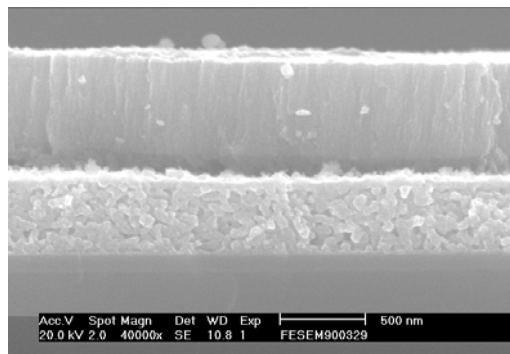


圖4-2 不同厚度 SnO_2 薄膜與LSCNO異質接合之表面及其橫截面之SEM顯微結構(a、b)400nm，(c、d)800nm

異質接合之幾何型態如下圖：

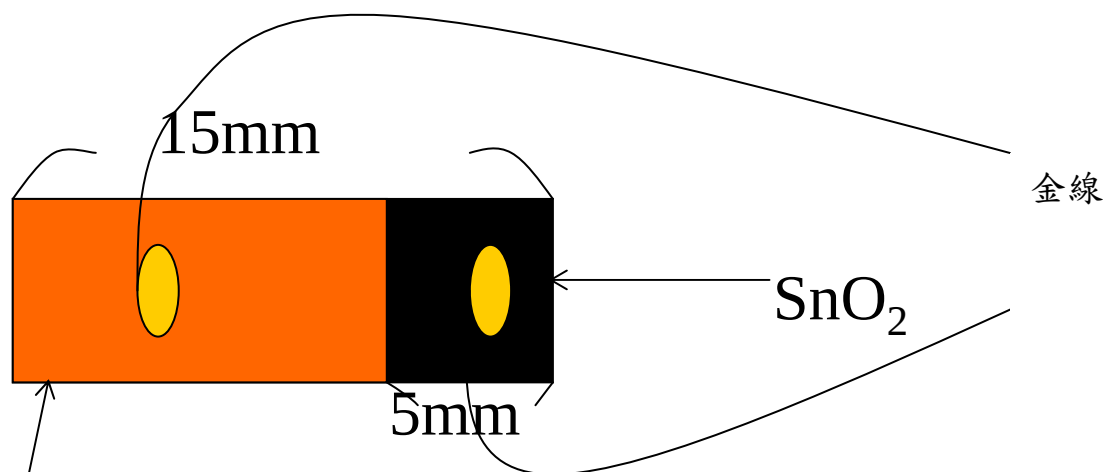
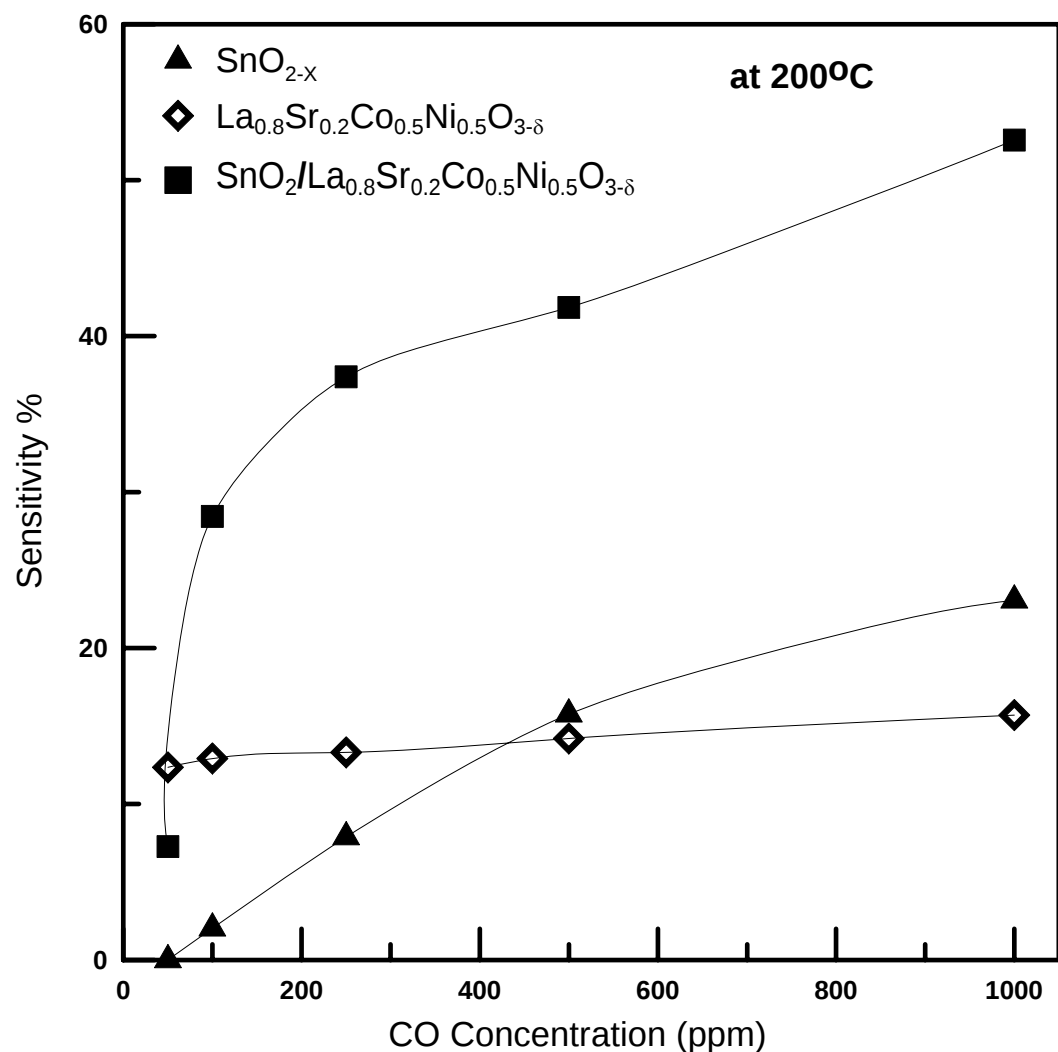


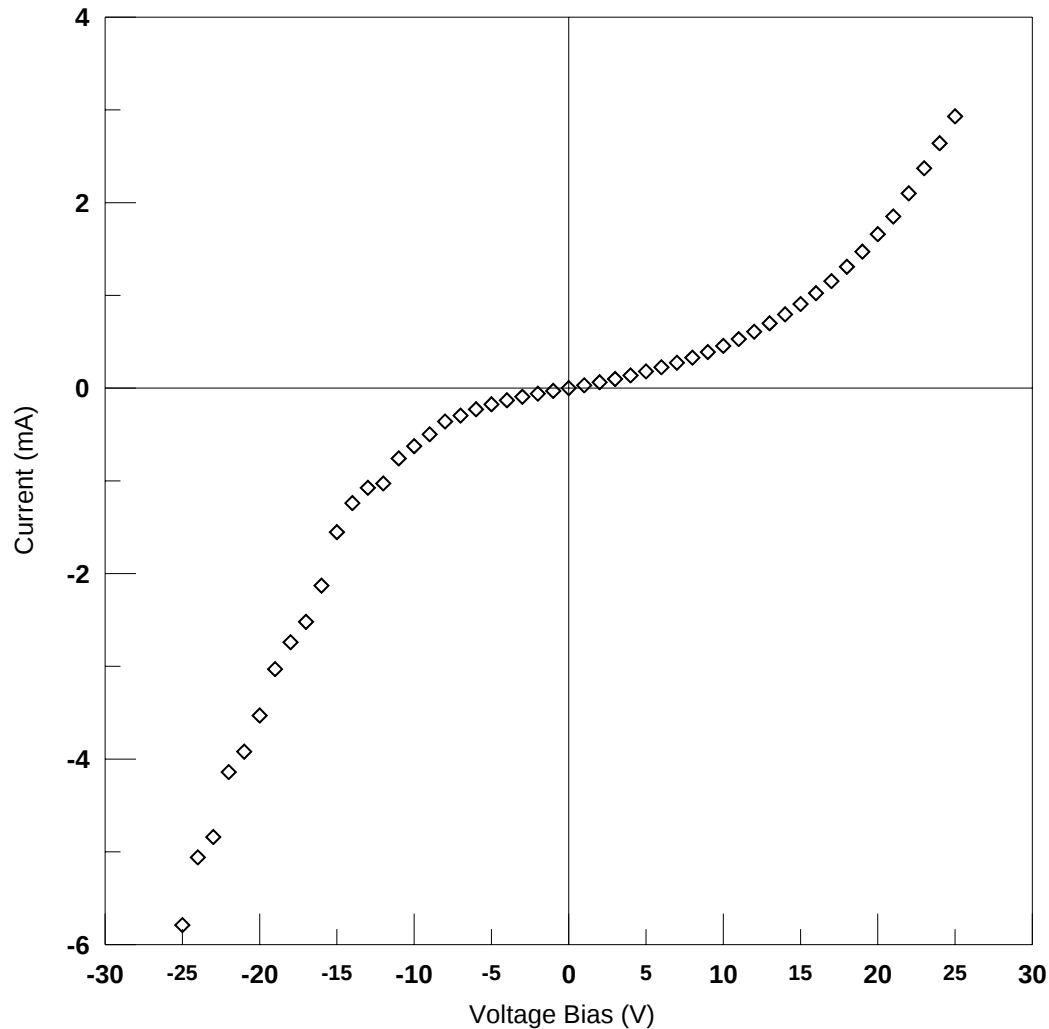
圖3-1 測試用試片之簡圖



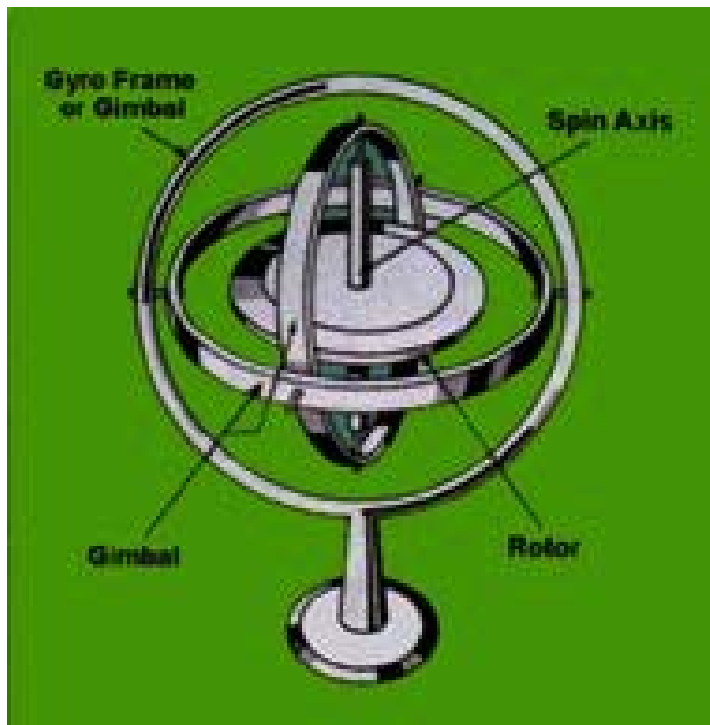
單層氧化物薄膜與異質接合薄膜 對CO感測特性之比較



SnO₂/LSCNO 異質接合薄膜在室溫下之I-V曲線



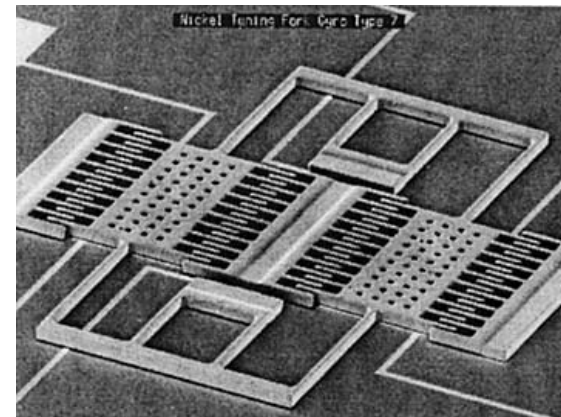
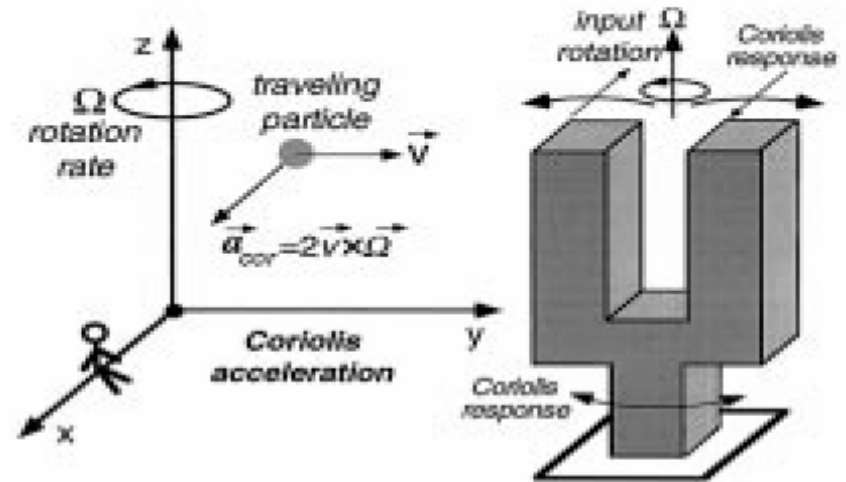
Gyroscopes



(株) シリコンセンシングシステムズジャパン

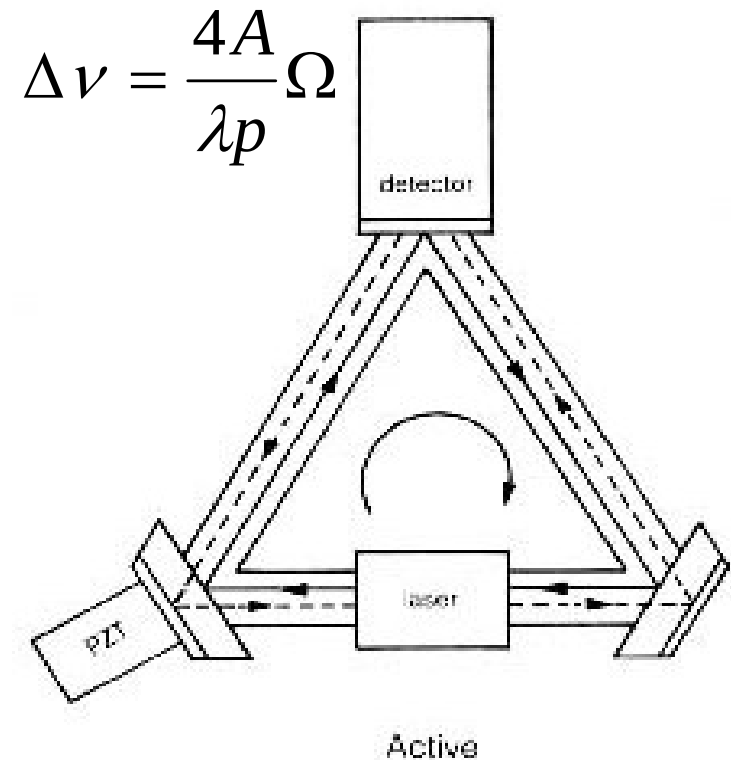
Draper Tuning Fork Gyro

- The rotation of tines causes the Coriolis Force
- Forces detected through either electrostatic, electromagnetic or piezoelectric.
- Displacements are measured in the Comb drive



Laser Ring Gyroscopes

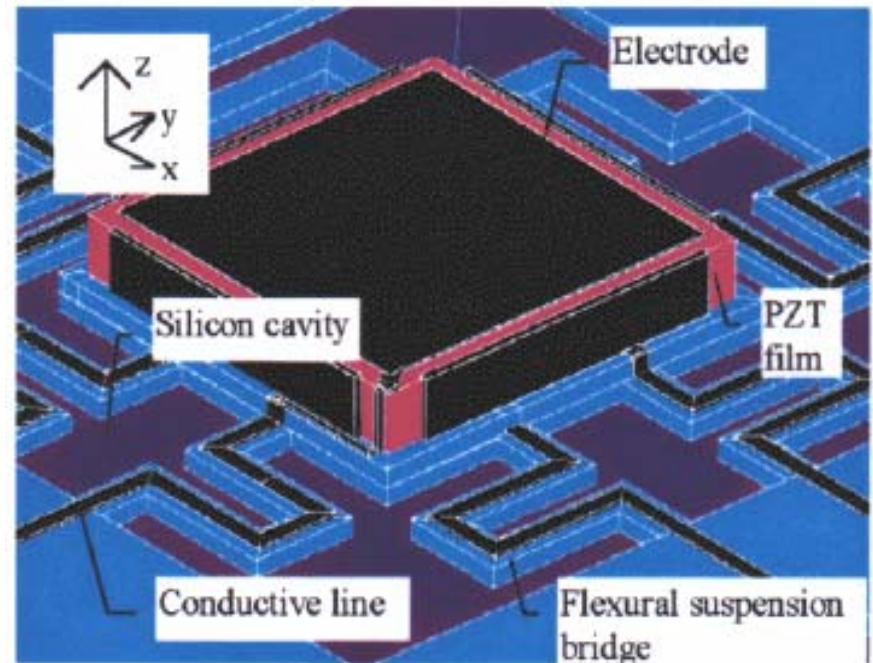
- Two signals sent around ring
- Different path lengths create a beat frequency.



- A – area of ring
- P – perimeter of ring

Piezoelectric Gyroscopes

- Basic Principles
 - Piezoelectric plate with vibrating thickness
 - Coriolis effect causes a voltage from the material
 - Very simple design and geometry



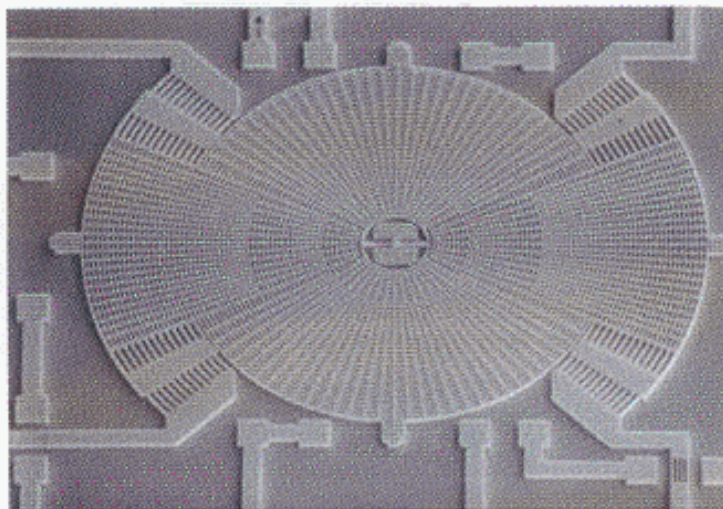


Fig. 1a: Gyrometer chip manufactured using the described Bosch Si-surface micromachining process.

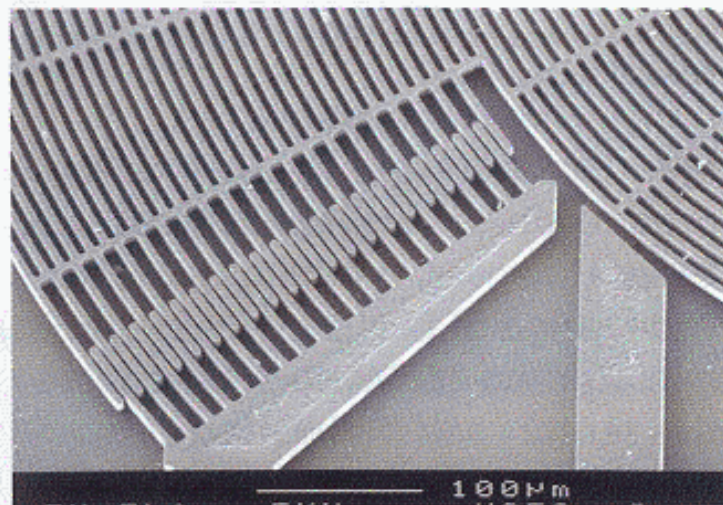
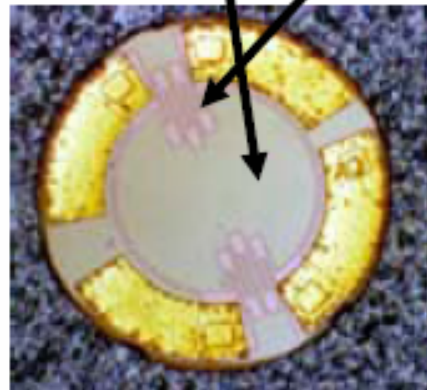
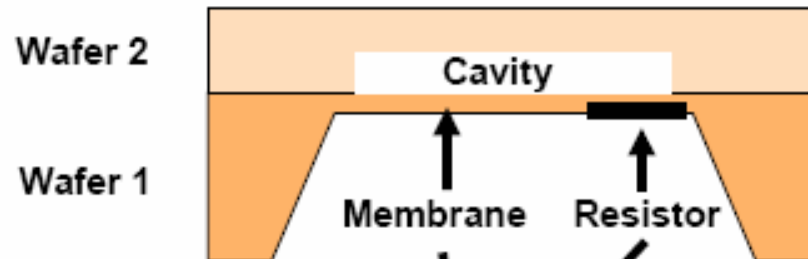


Fig. 1b: Details of an accelerometer comb-structure.

Applications of gyroscope

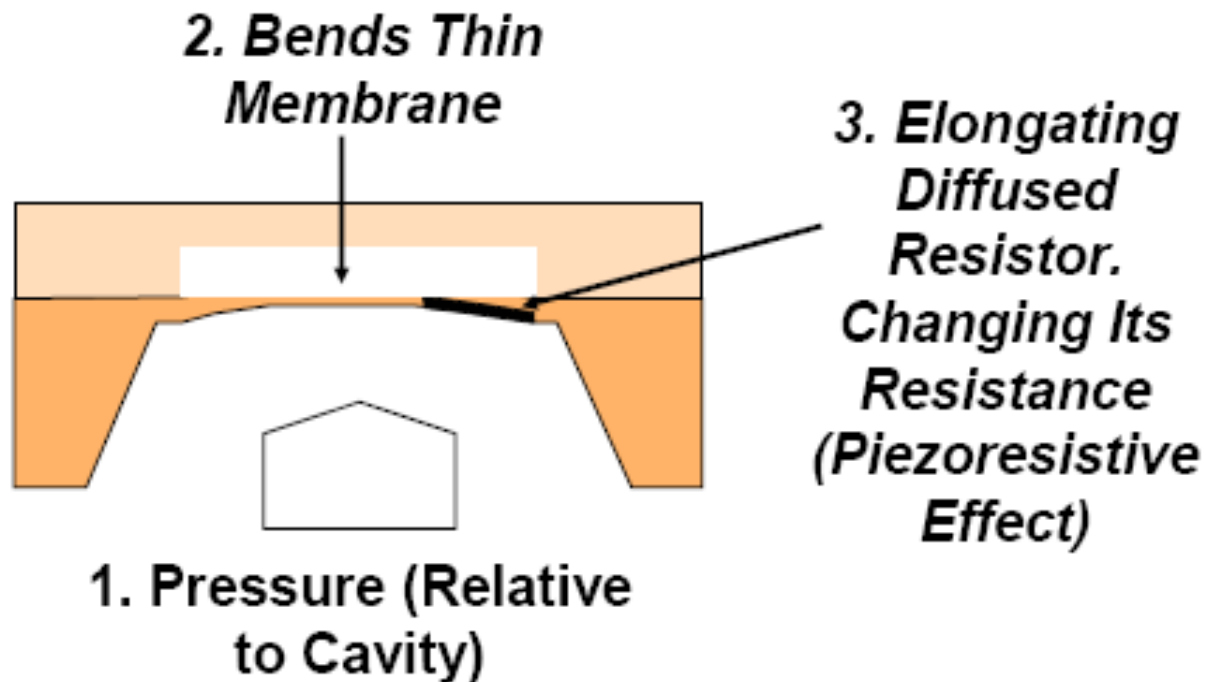
- * Anti-Lock Brakes
- * Military Munitions
- * Inertial Measurement Unit
- * Gait-Phase Detection Sensor
Embedded in a Shoe Insole

Micromachined Pressure Sensor



Motorola

Operation of pressure sensor



Accelerometer

MEMS accelerometers market

- Success of MEMS accelerometers is pushed by a general growth of all the marketplaces.

Year	1996	2002	2005	2008
Market size	240 M\$	400 M\$	560 M\$	800 M\$

Annul growth

+10%

+12%

+12%

– Automotive : 80%

– Seismic : 3%

– Avionic and defense : 8%

– Tilt et stabilization : 2.5%

– Agriculture : 3%

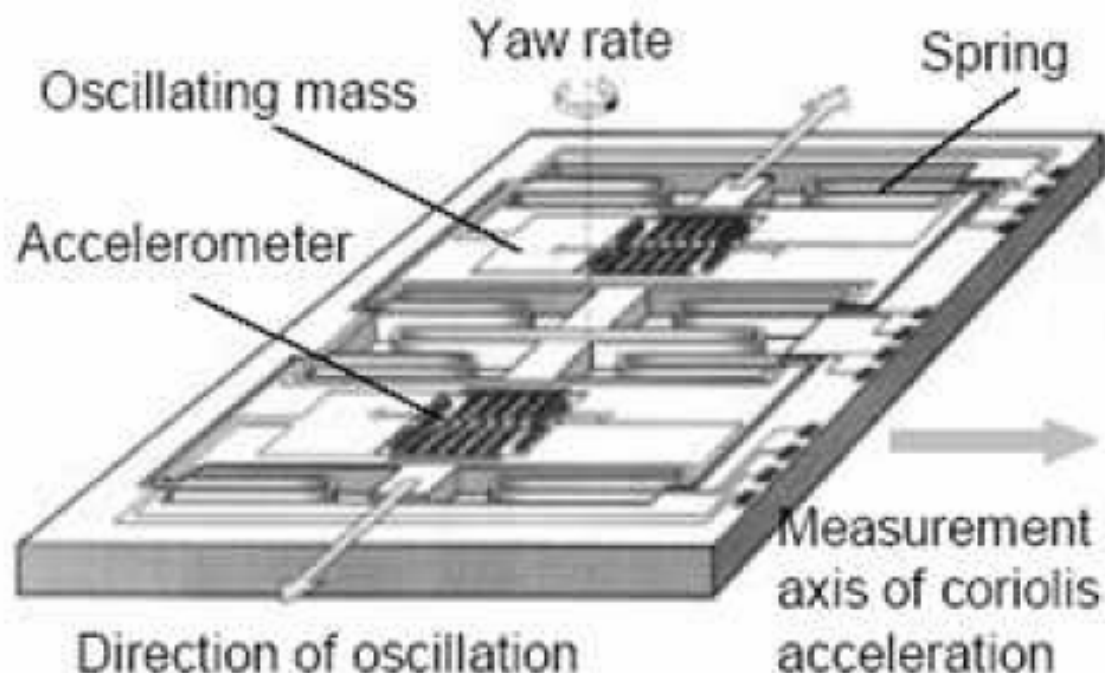
– Various : 3.5%

Values inherited from following market studies:

- NEXUS: "market studies from 1996 to 2002"
- Intechno Consulting's: "Sensor Markets 2000"
- Yole: "World MEMS inertial sensors"



iMEMS® Accelerometer



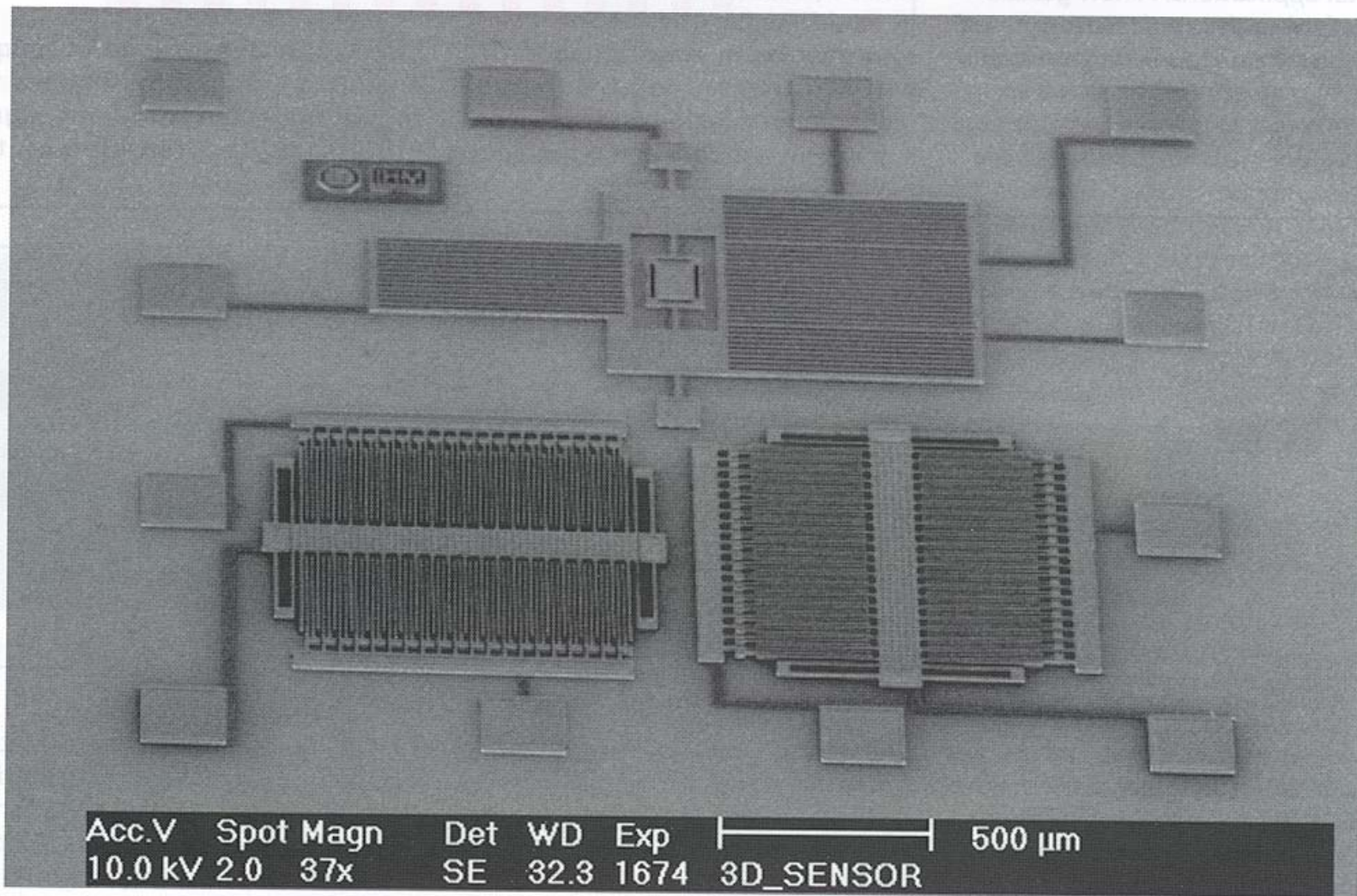
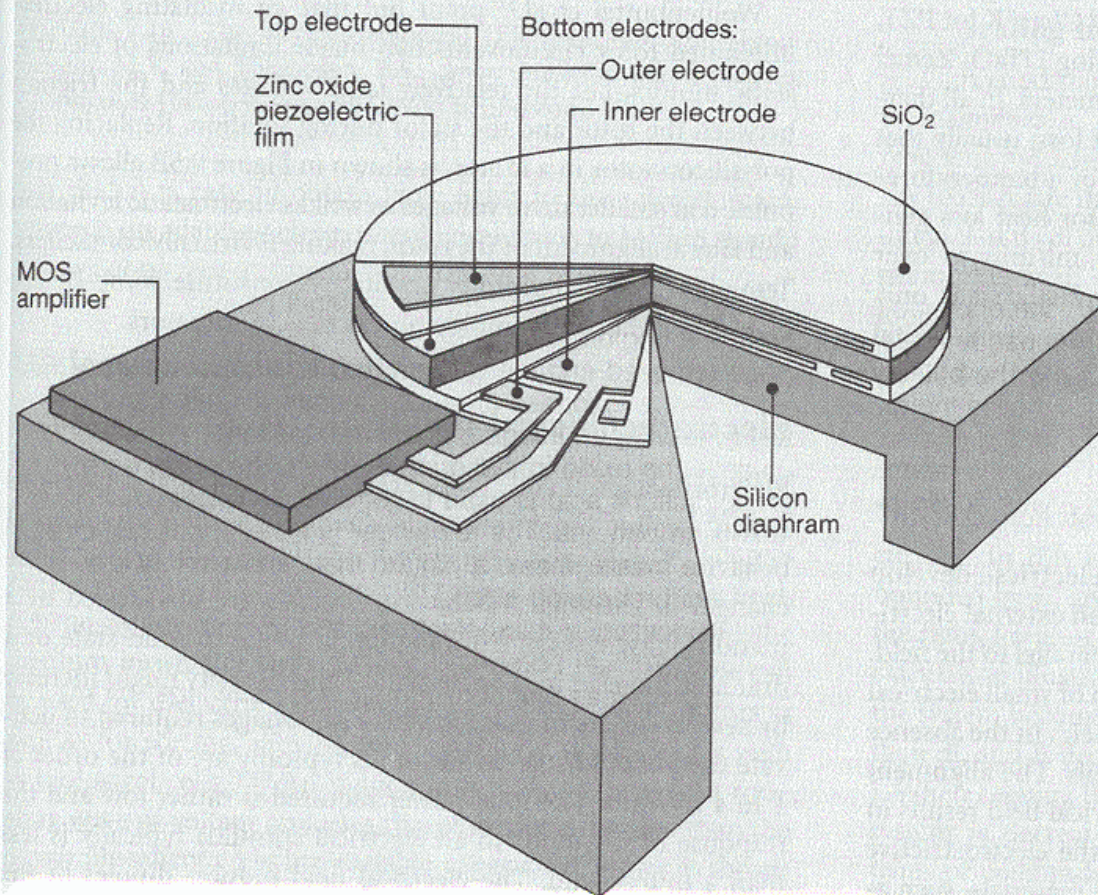
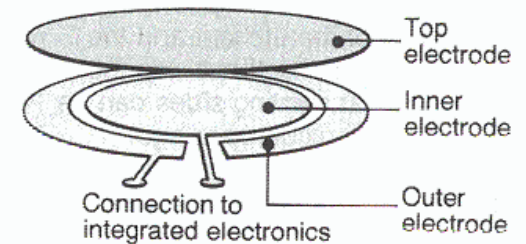


Fig. 4: 3D accelerometer micromachined by the author in Dresden University of Technology, Dresden, Germany.

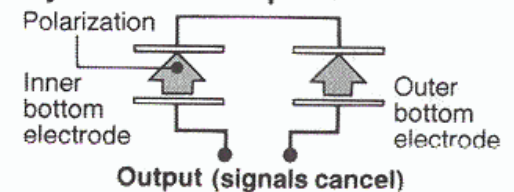
Zinc oxide acoustic sensor



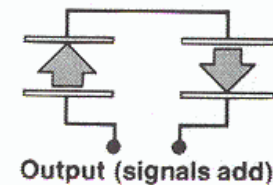
A



Pyroelectric response



Piezoelectric response



B

FIGURE 9.9 Zinc oxide acoustic sensor. Two parallel plate electrodes in Honeywell's acoustic sensor act as capacitors. Voltages due to temperature variations (pyroelectric effect) on zinc oxide film cancel, while those due to pressure add, doubling the output. (From Allen, R., *Sensors in Silicon*, *High Technology*, 43–81, 1984. With permission.)

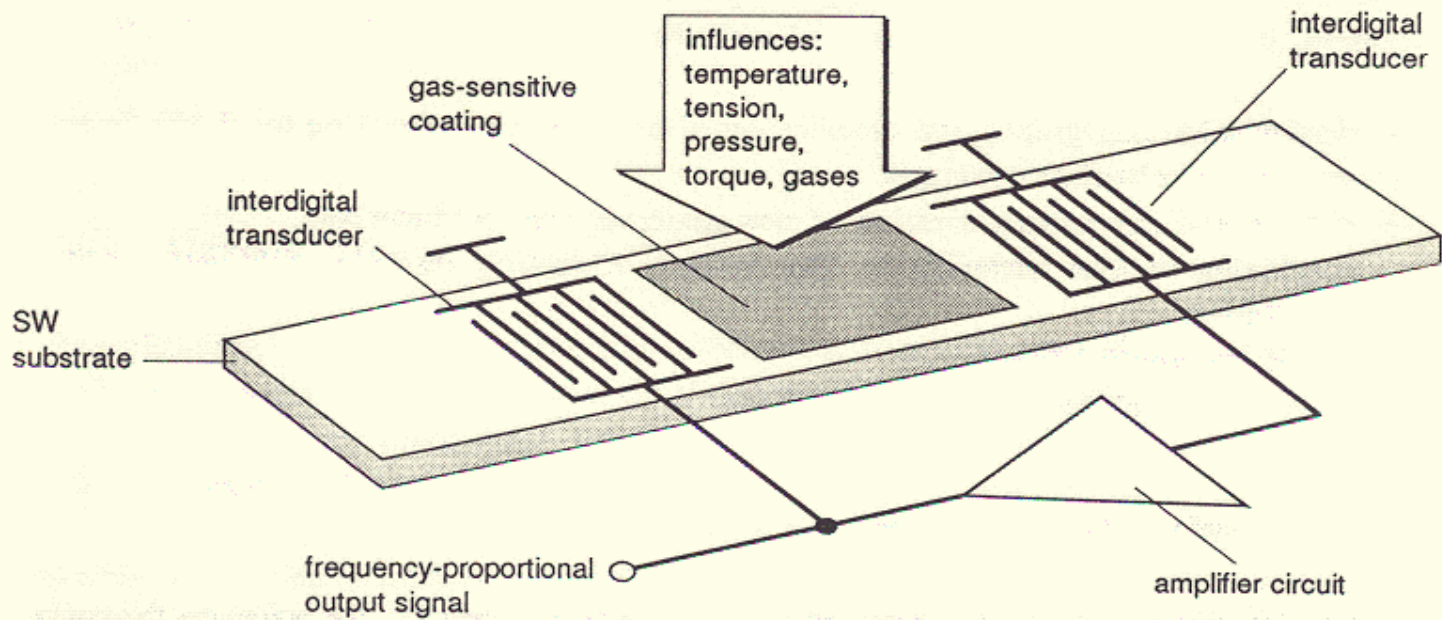


Figure 1-2. SW (surface-wave) sensors: changes in the parameters of SW propagation are converted into frequency changes of an oscillator.

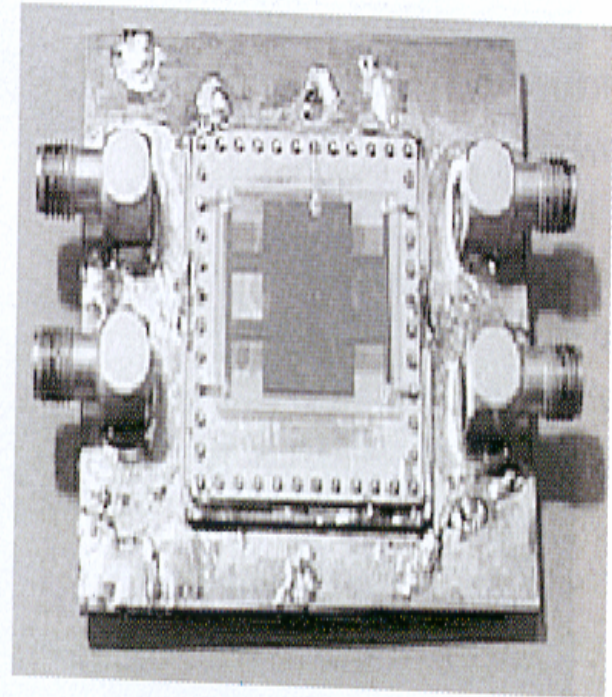
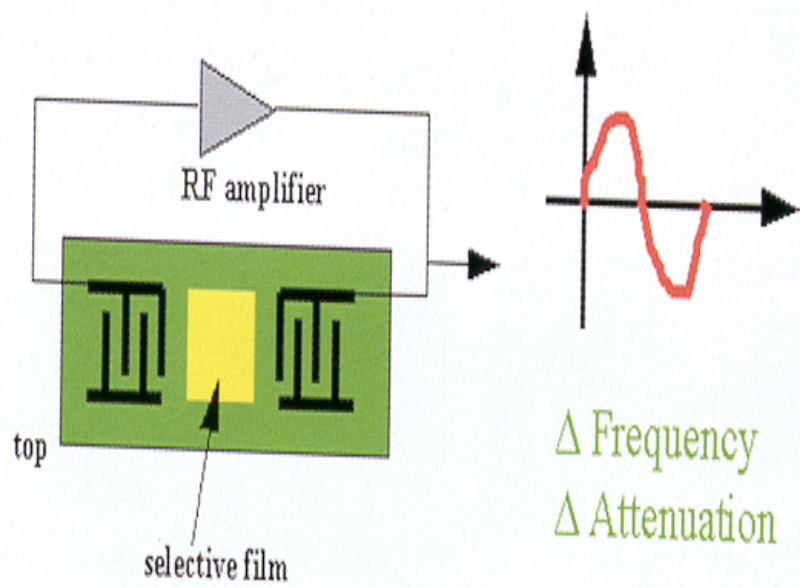


Fig. 1: Principle and assembly of a SH-SAW sensing device.

Actuators

Micromotors: Electrostatic,
Electromagnetics.....

Diaphragm pump

Micro-tweezer

Ink jet

Magnetic head driver

.....

微型制動器使用之材料：

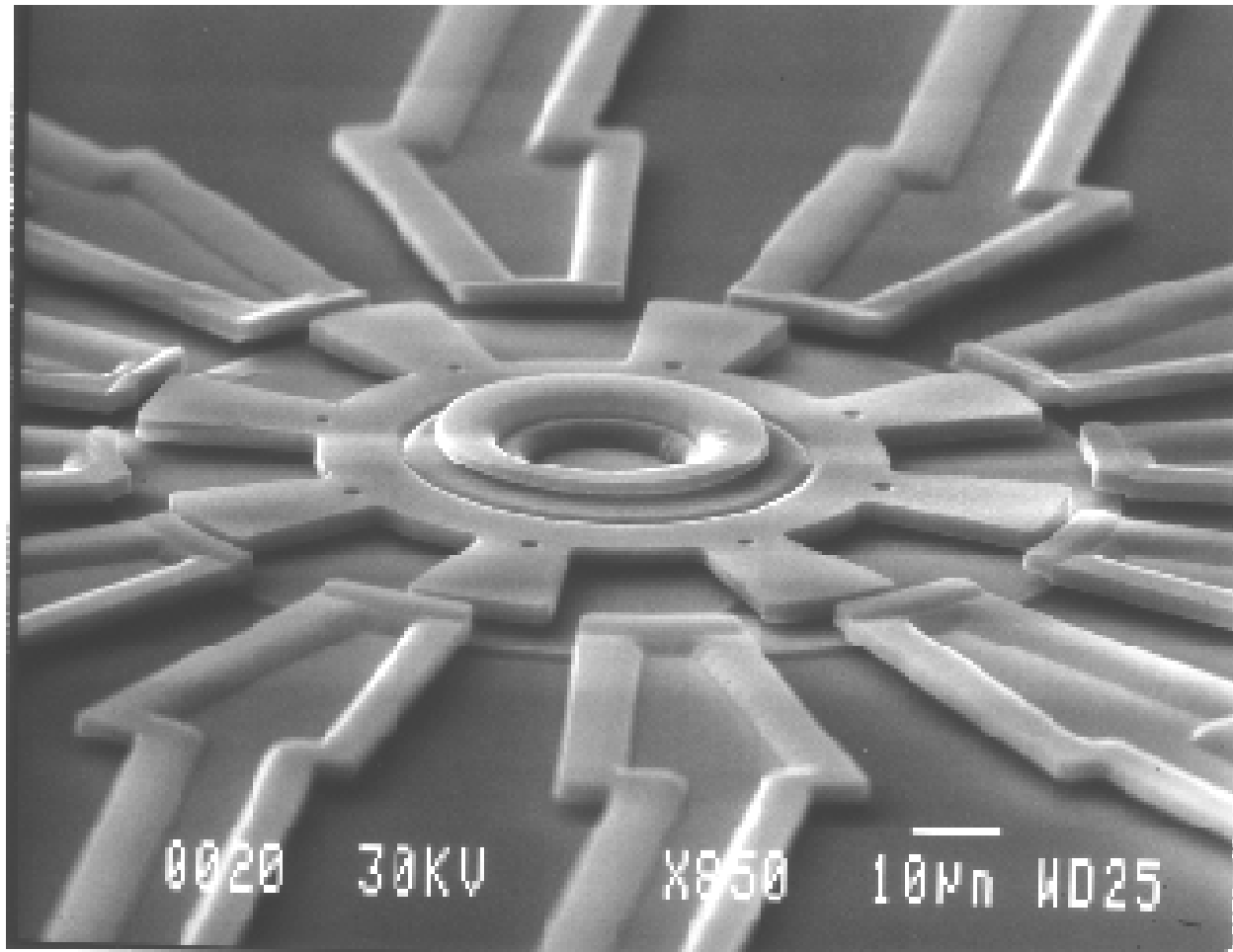
電磁式---軟硬磁組合，磁伸縮材料

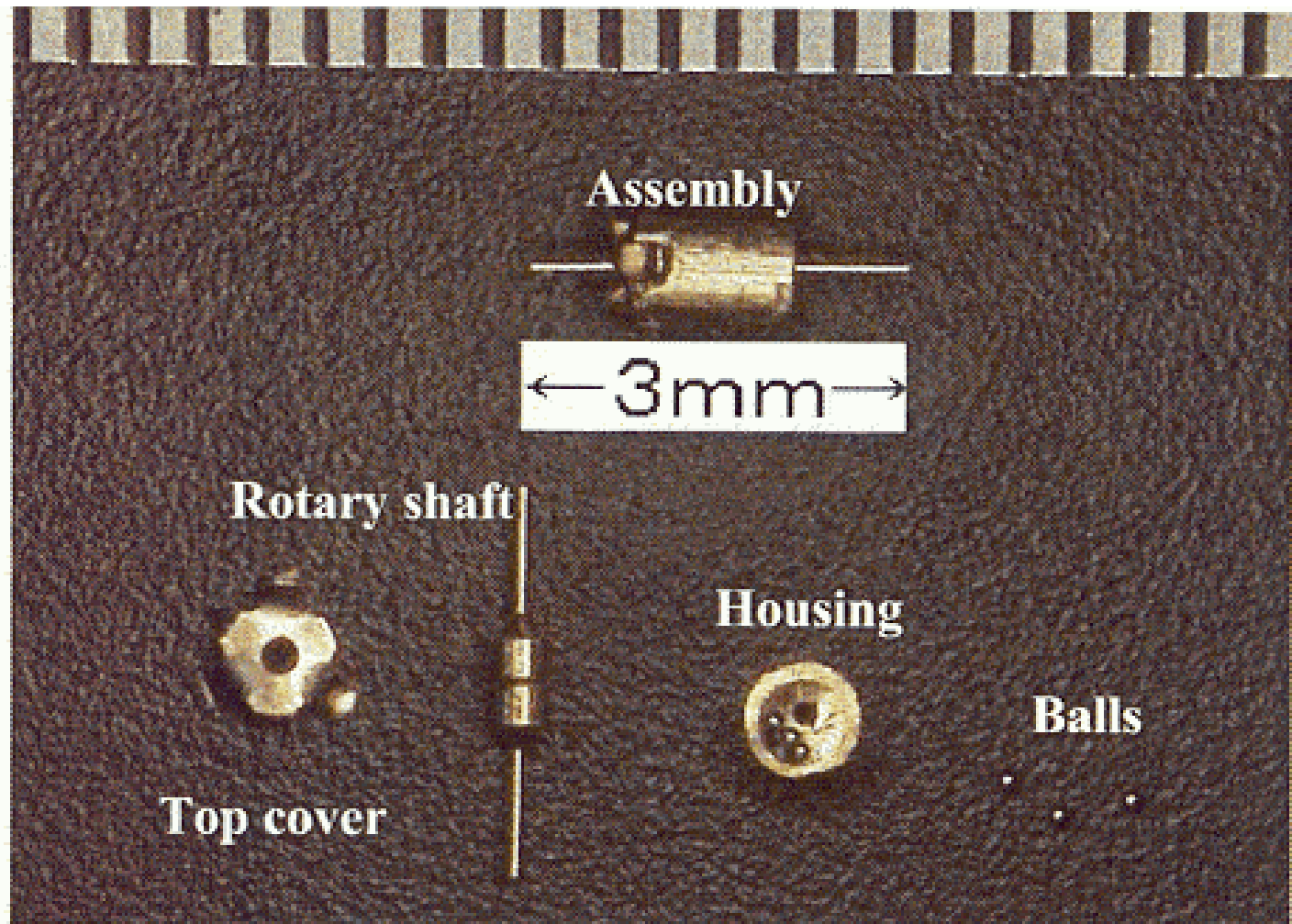
壓電式---PZT

SMA----TiNi alloy

熱驅動式--- Bimetal （熱膨脹式）

Electrostatic motor





Diaphragm pump

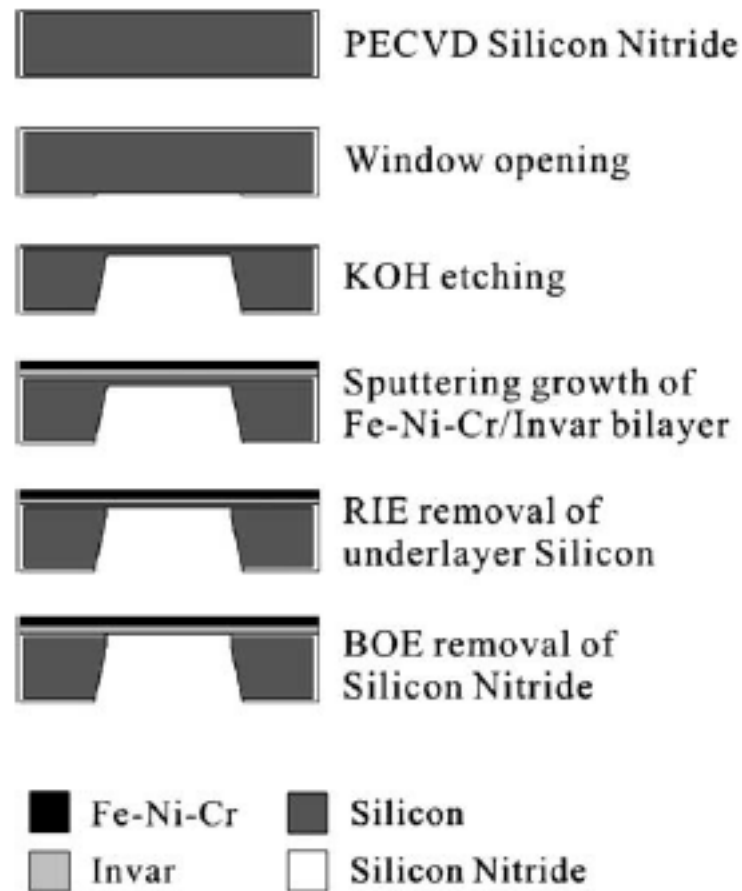


Fig. 1. Fabrication process for freestanding membrane.

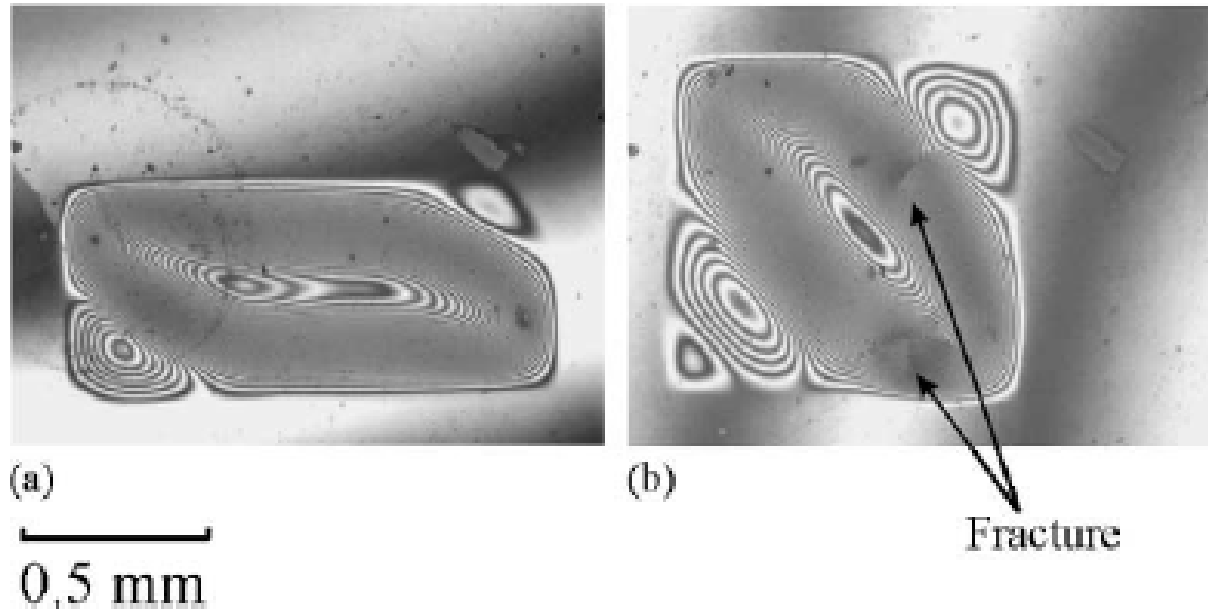
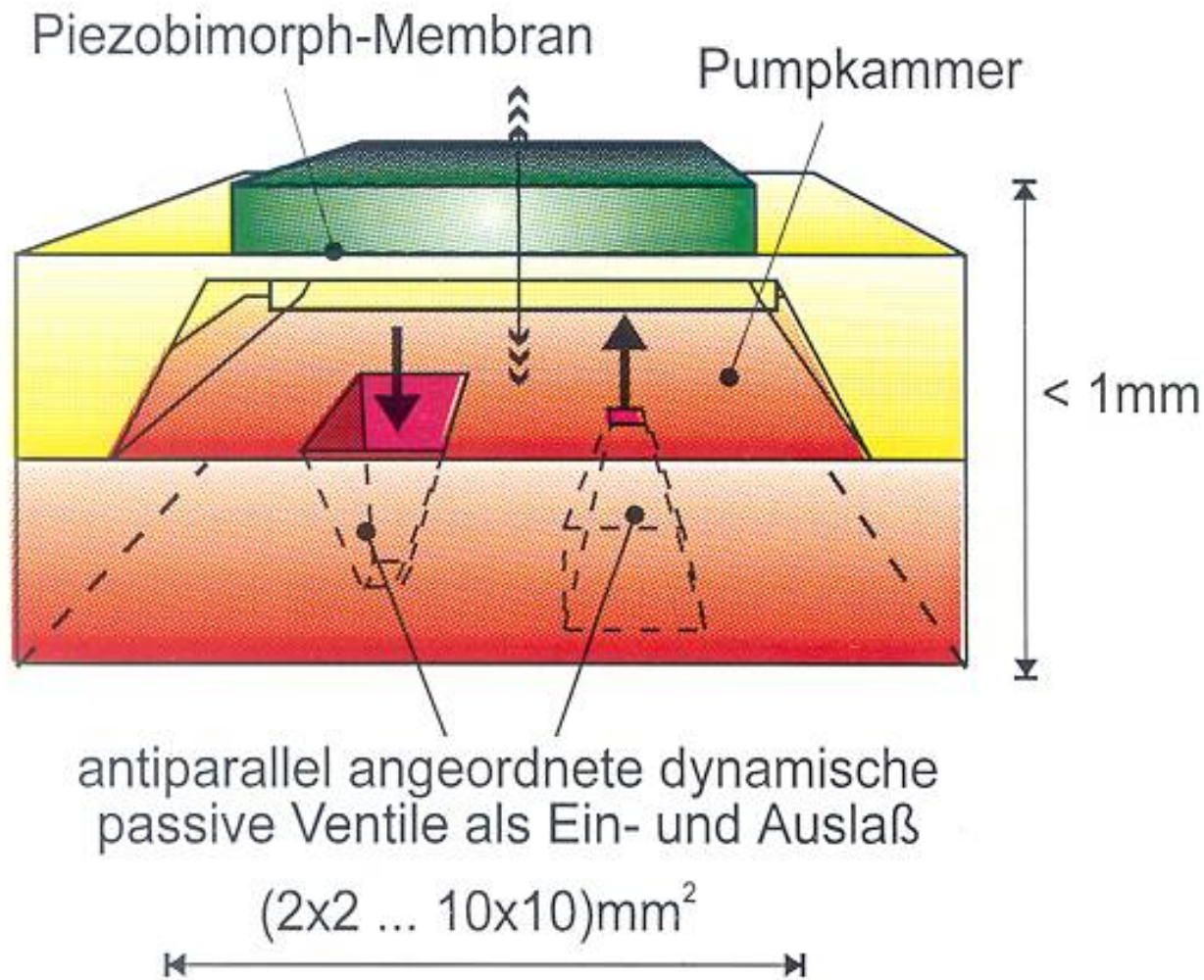


Fig. 4. Compressive residual stress induced postbuckling and fracture for the freestanding bimetal membrane. Top-view of the FNC (upper layer)/Invar membrane: (a) 40 mTorr deposition pressure; (b) 25 mTorr deposition pressure.

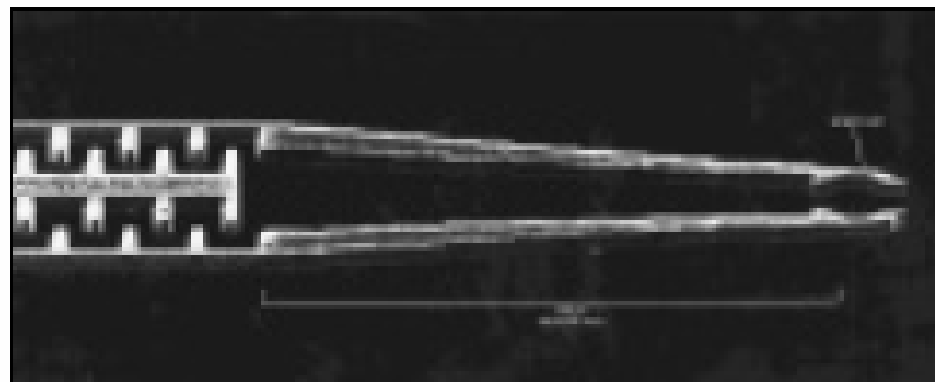
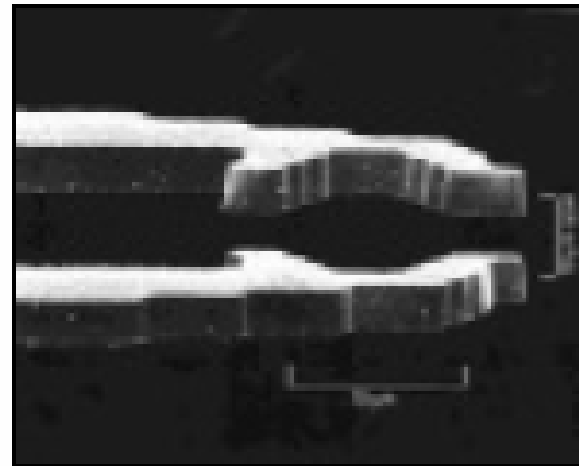
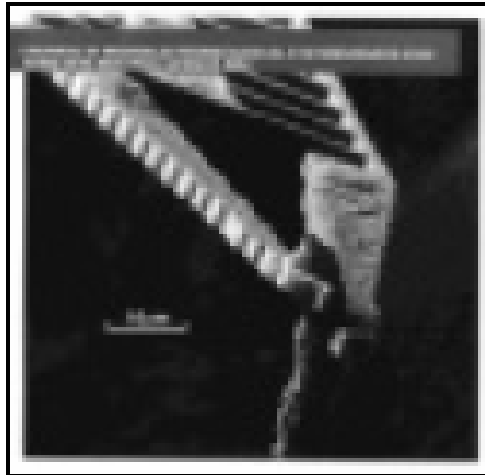
Performance parameters	This study	Other studies				
	FNC/Invar	Al/silicon [22]	Al/poly Si/silicon [4]	Ni/silicon [22]	SMA [23]	Al/SiN _x /poly Si/Si [24]
Power consumption (W)	0.1	0.5	*12 V	1.03	16	0.56
Active area for deflection (mm ²)	1	NA	9	64	25	16
Deflection (μm)	94		72	NA	100	5
Actuation speed (ms)	56	100	NA	200	100	NA
Package size (mm ³)	NA	6.8	NA	2.3	NA	NA

* The driving power was supplied through dc voltage pulses.

Micro-pump and valves

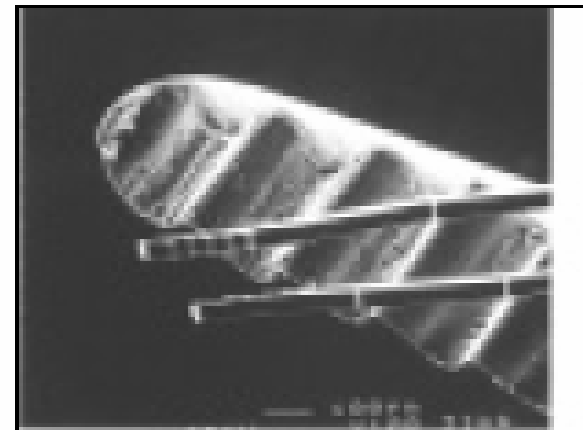
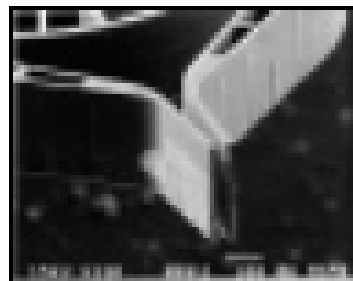
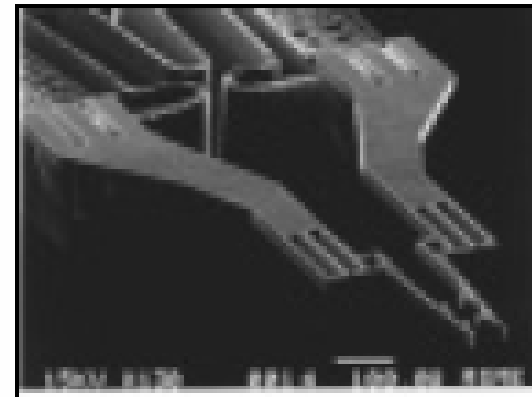
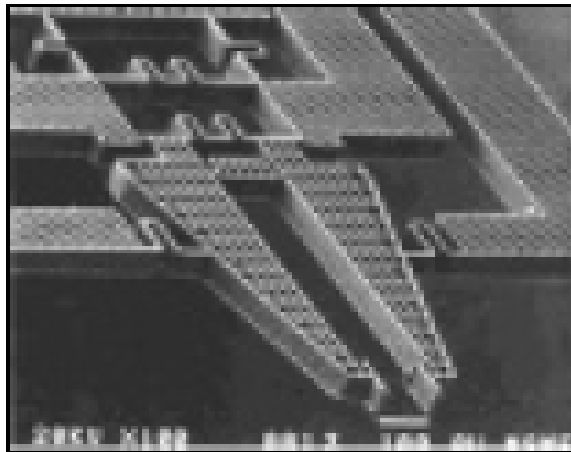


Micro-Grippers



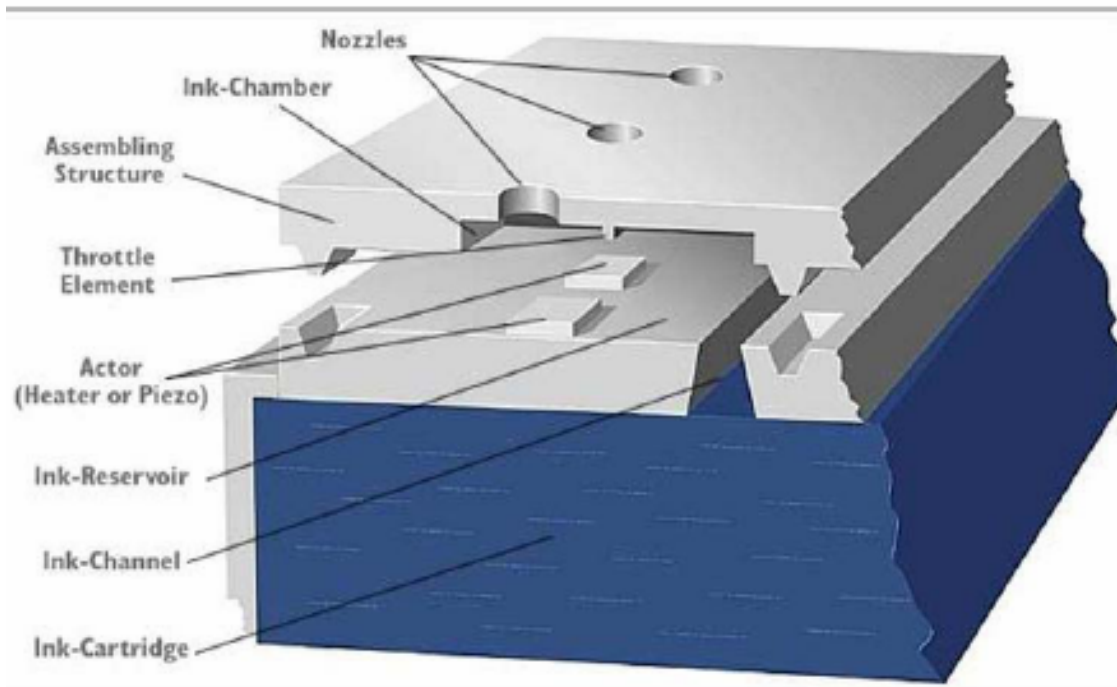
Source: Berkeley

Micro-Tweezers

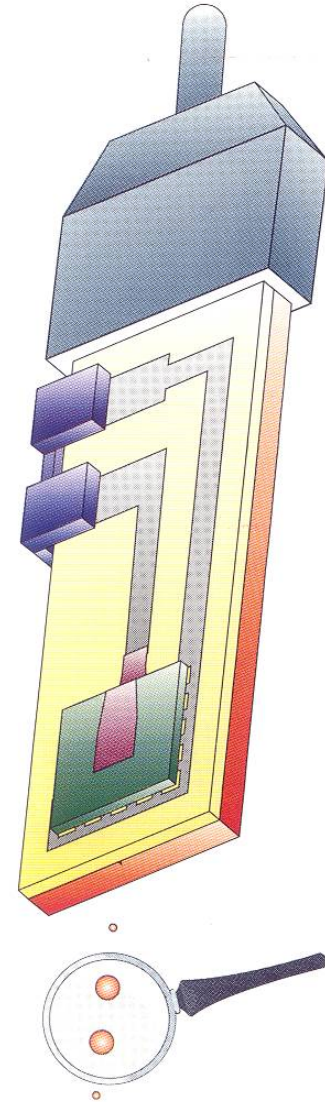
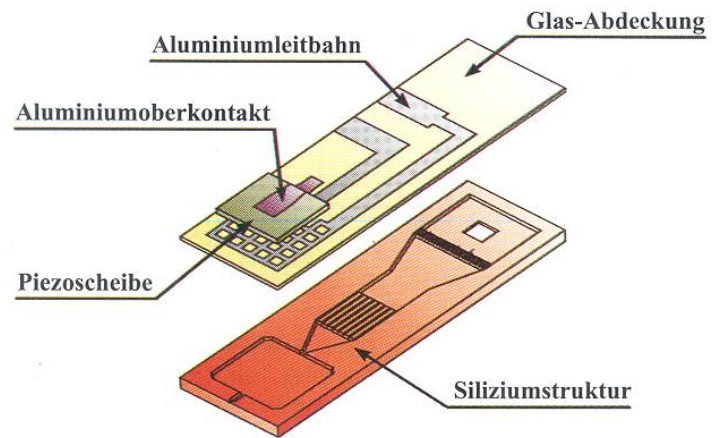


Source: MEMS Precision Instruments

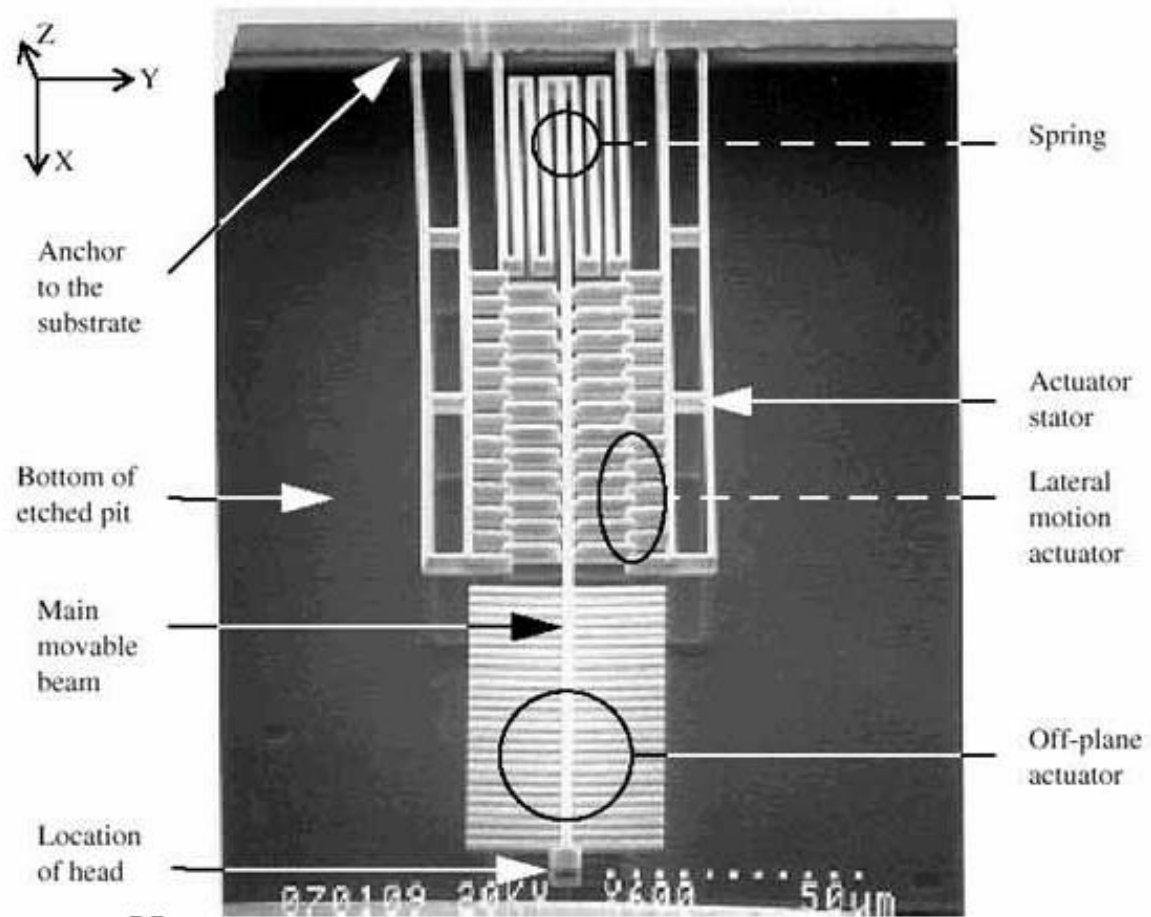
- Ink jet printers are **MEMS** based – late 1970's, IBM and HP



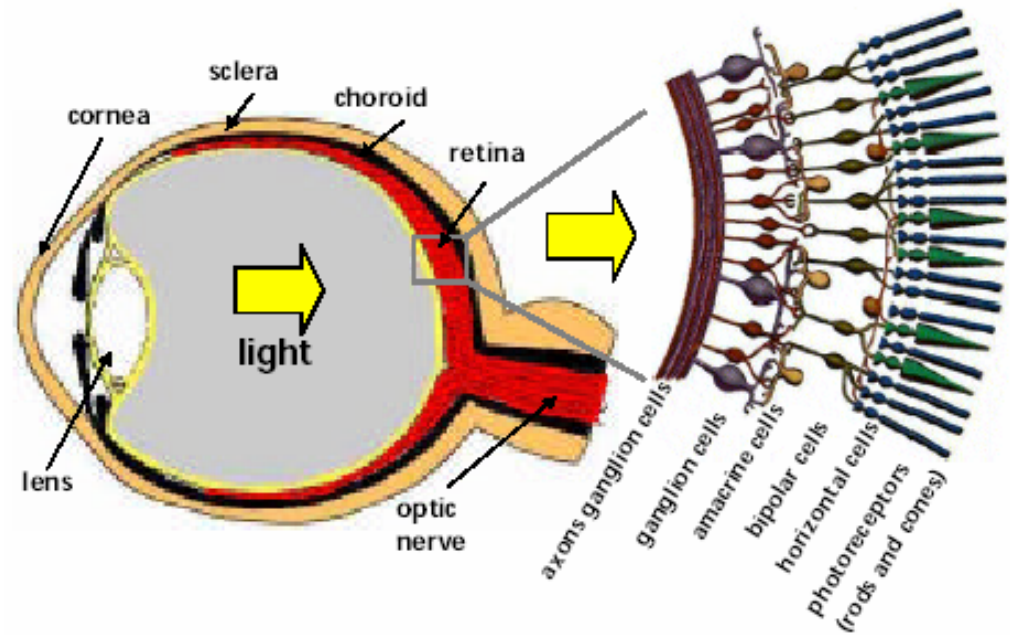
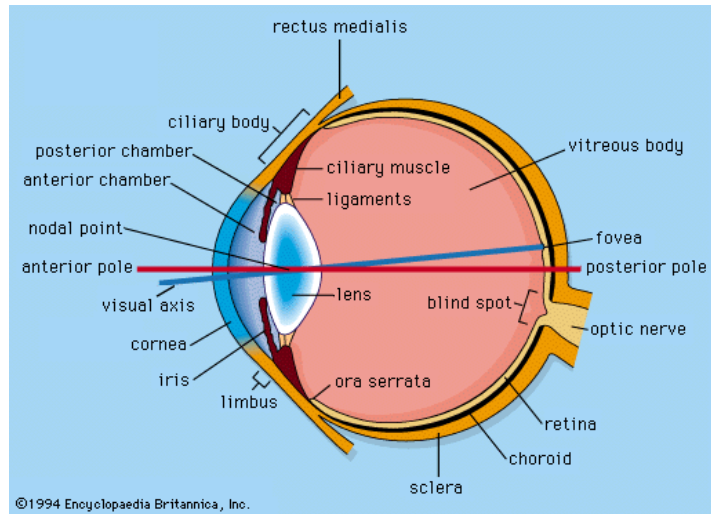
噴墨頭示意圖

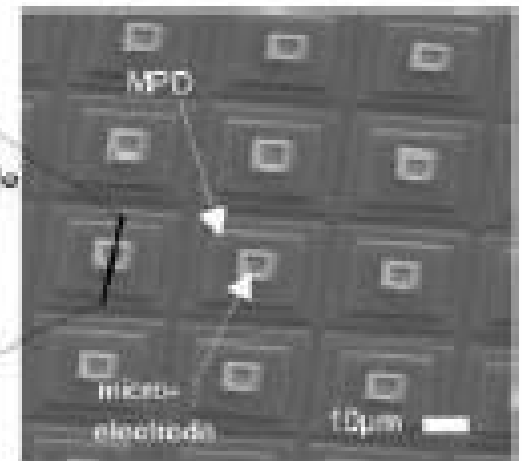
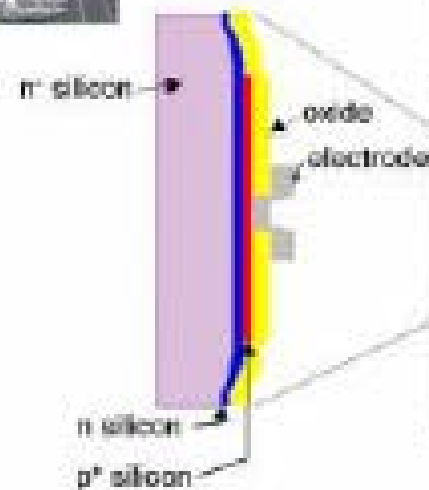
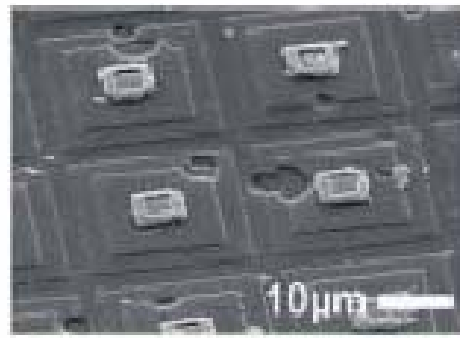
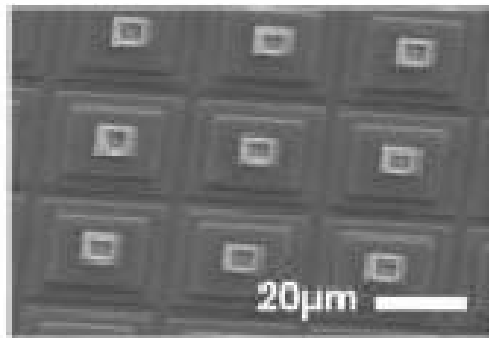
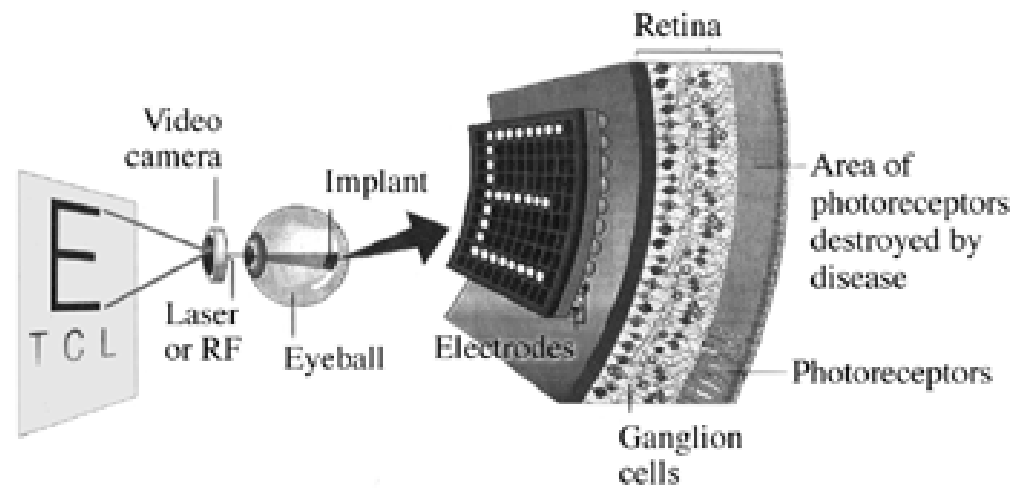


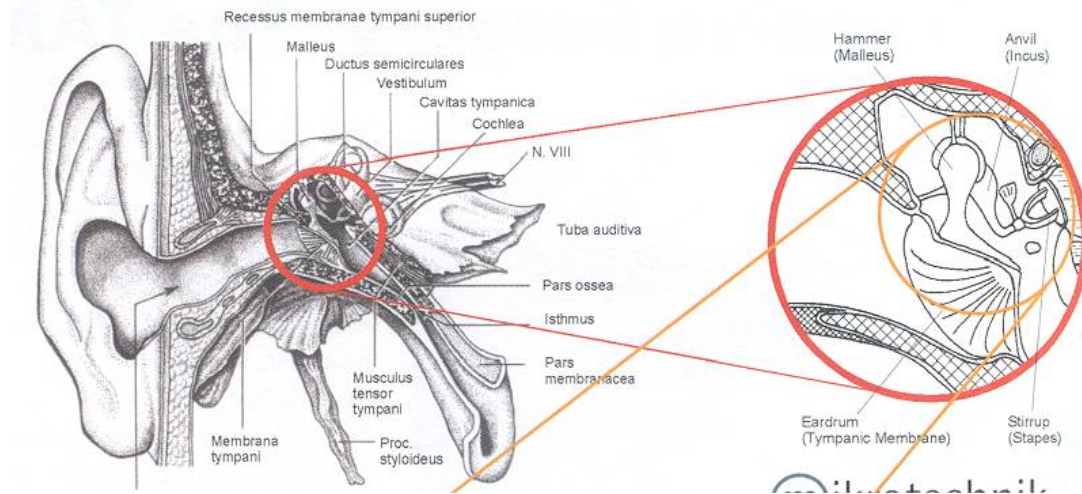
Magnetic read/write heads for hard drives.



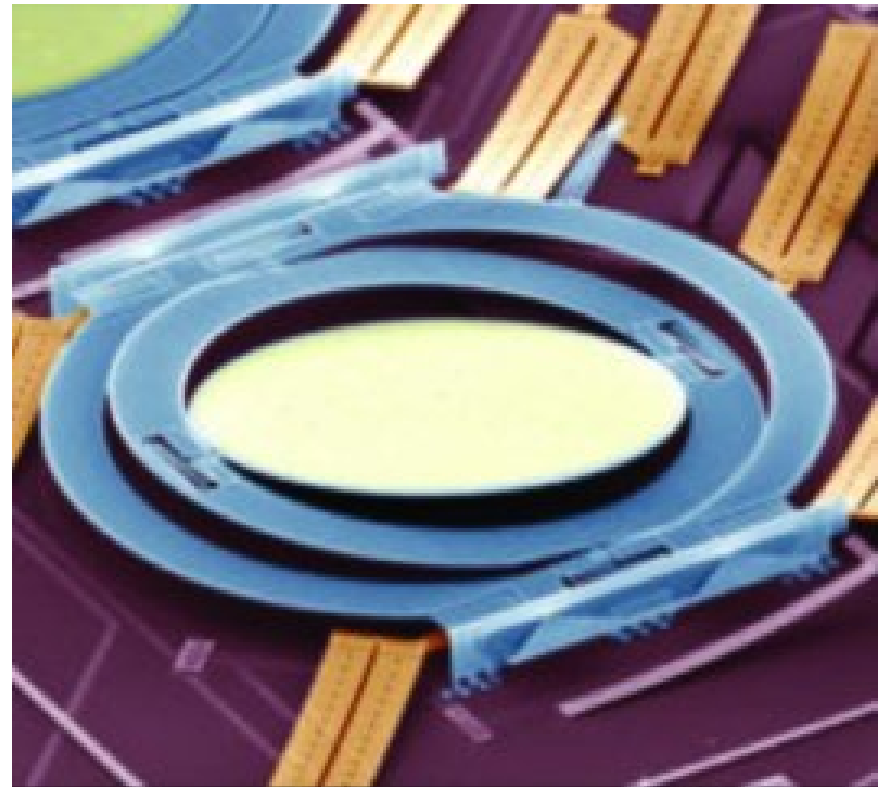
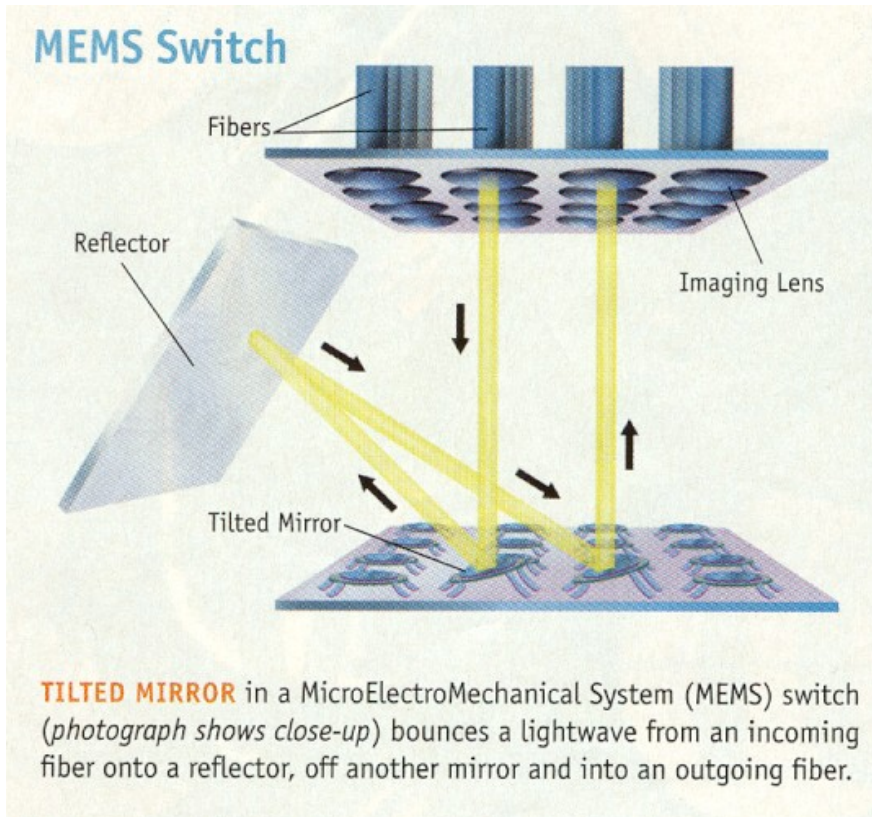
Optobionics: Retinal Implant

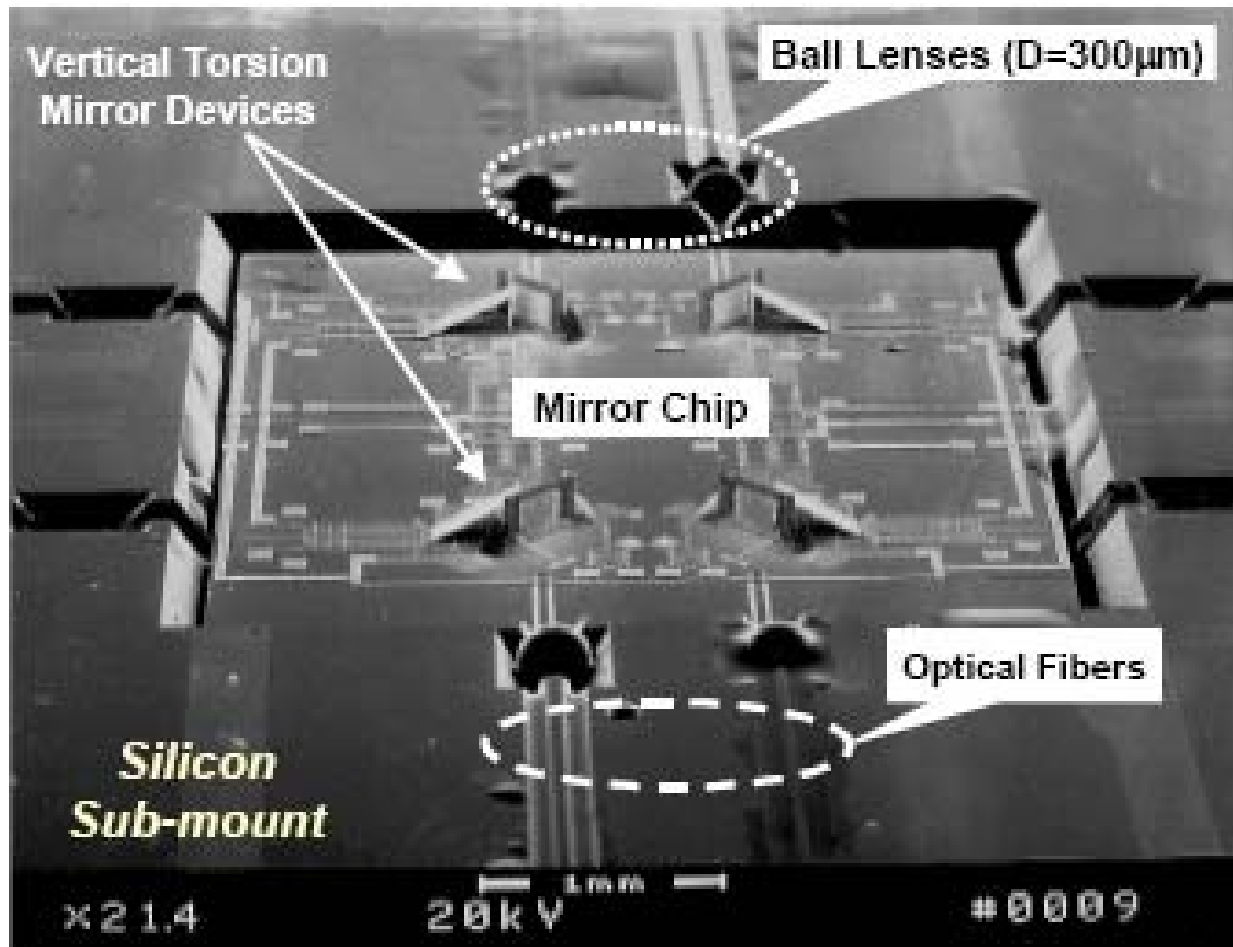


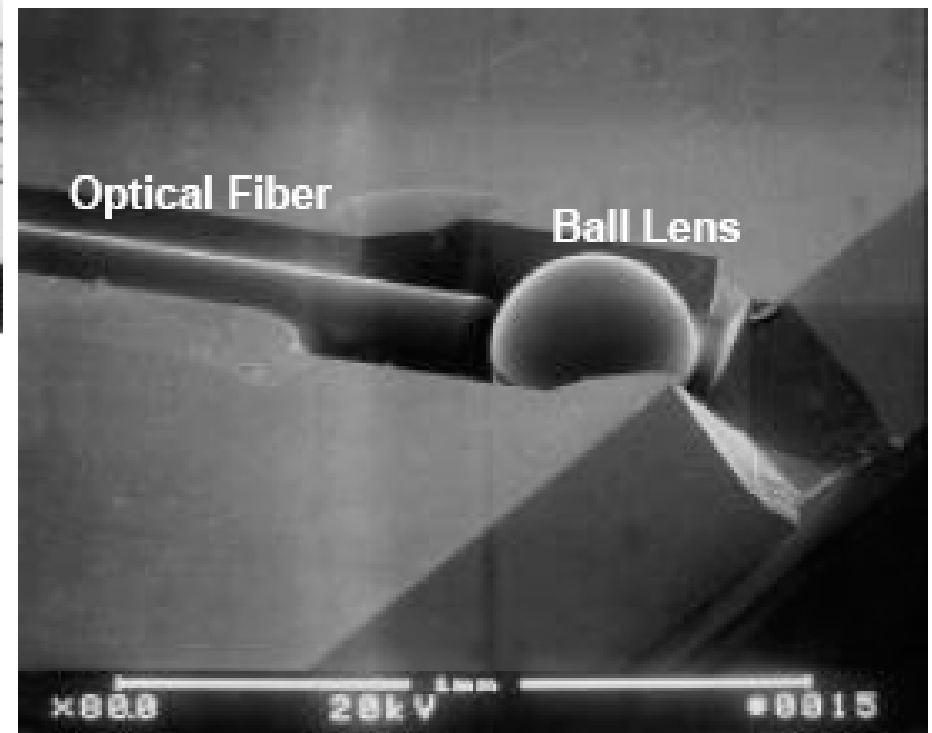
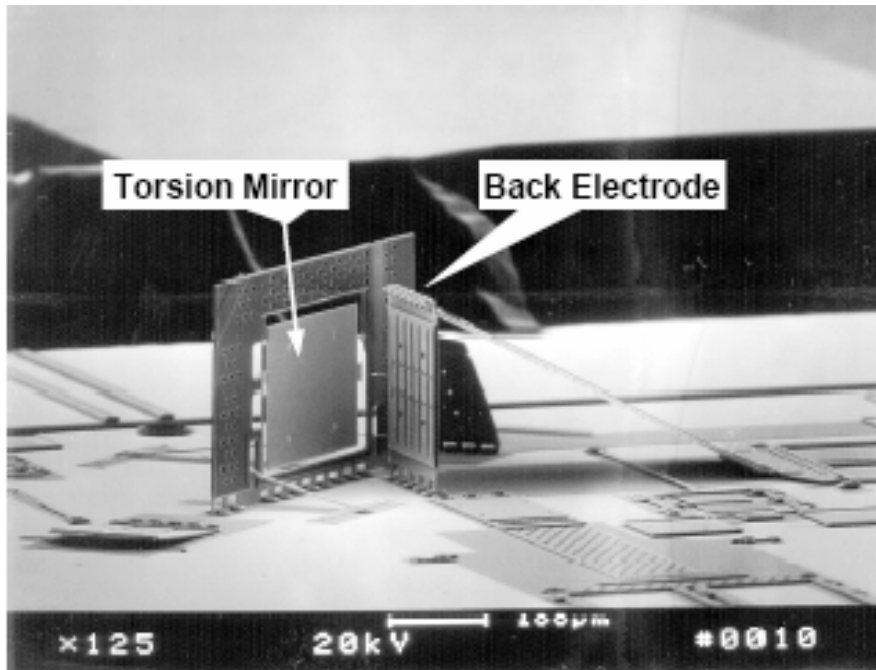




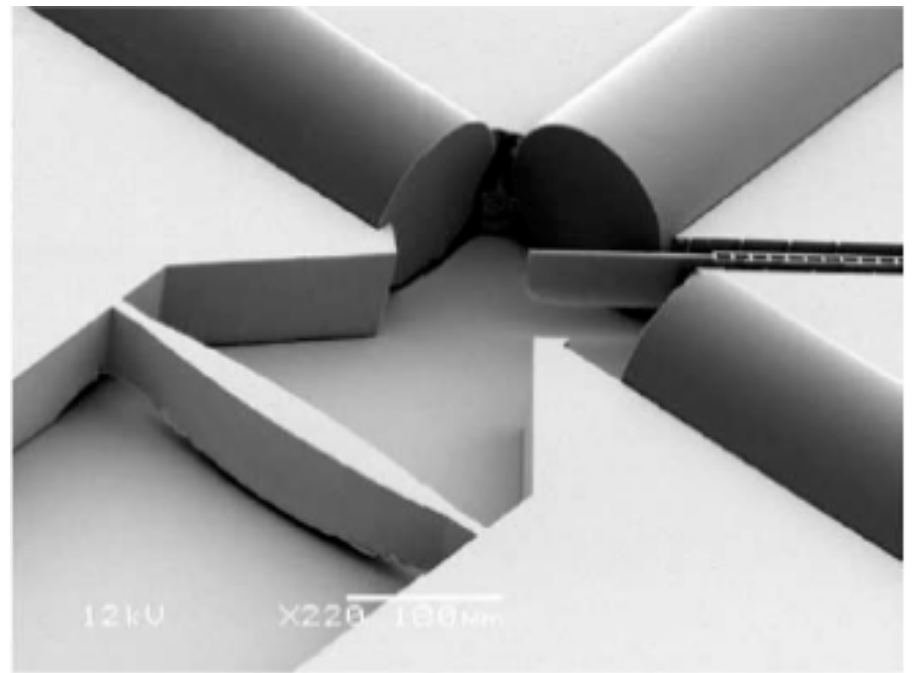
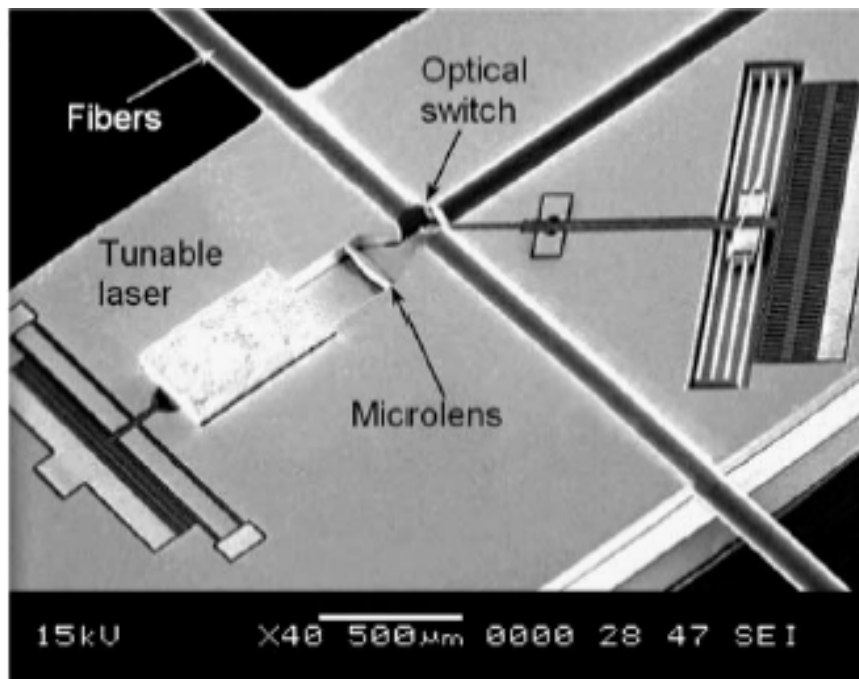
Two Axis Micro-mirror



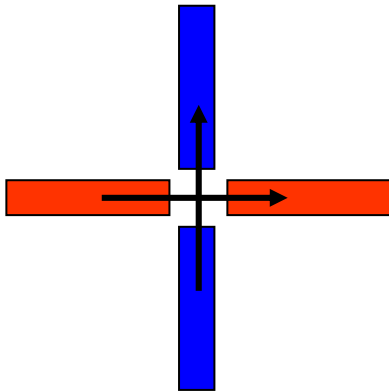




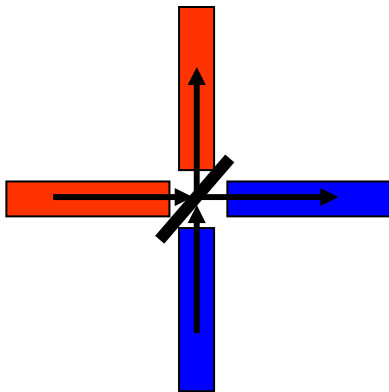
Optical Switch



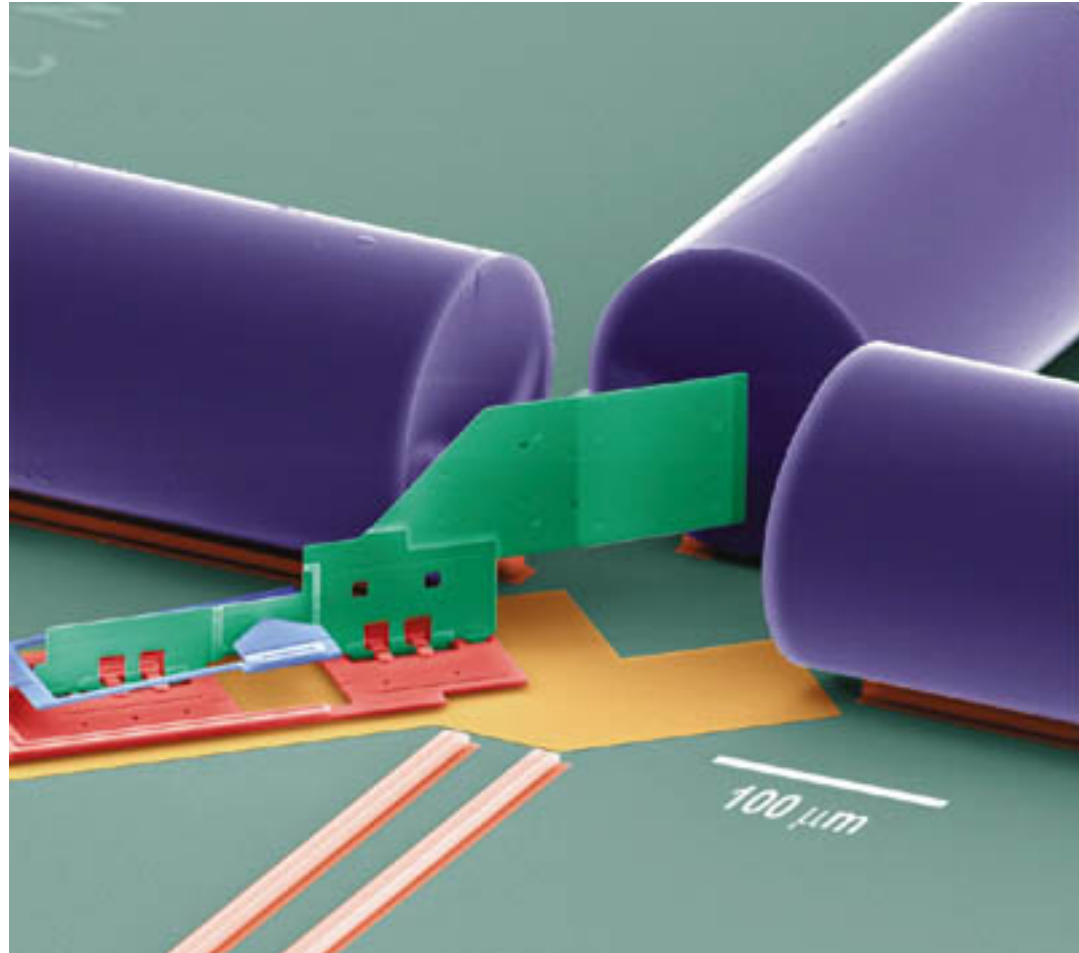
2x2 Optical Switch



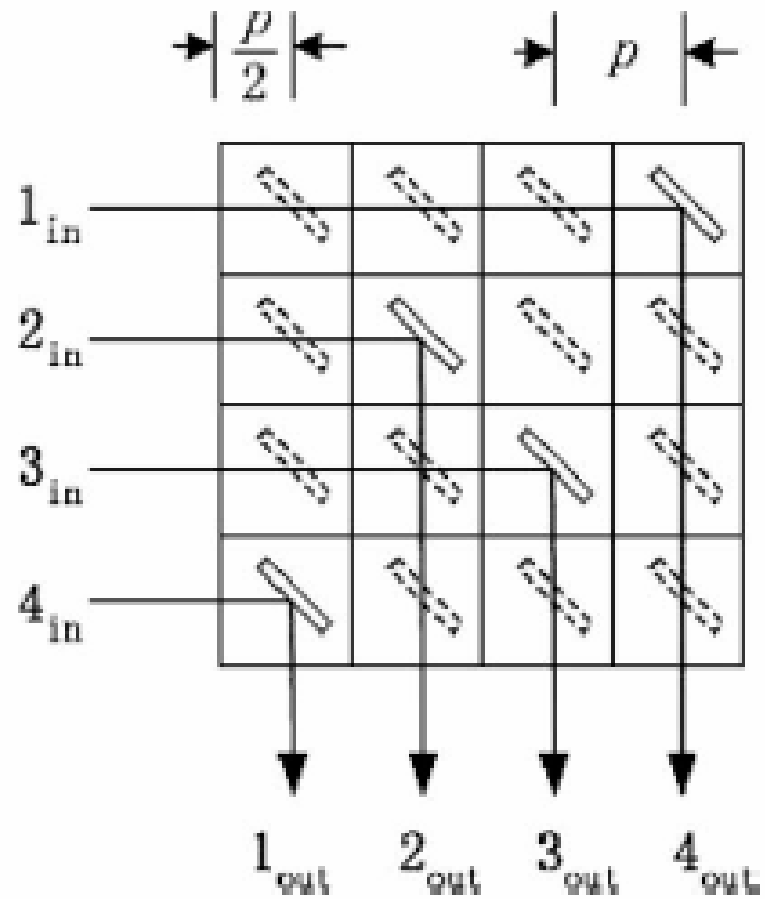
Cross State



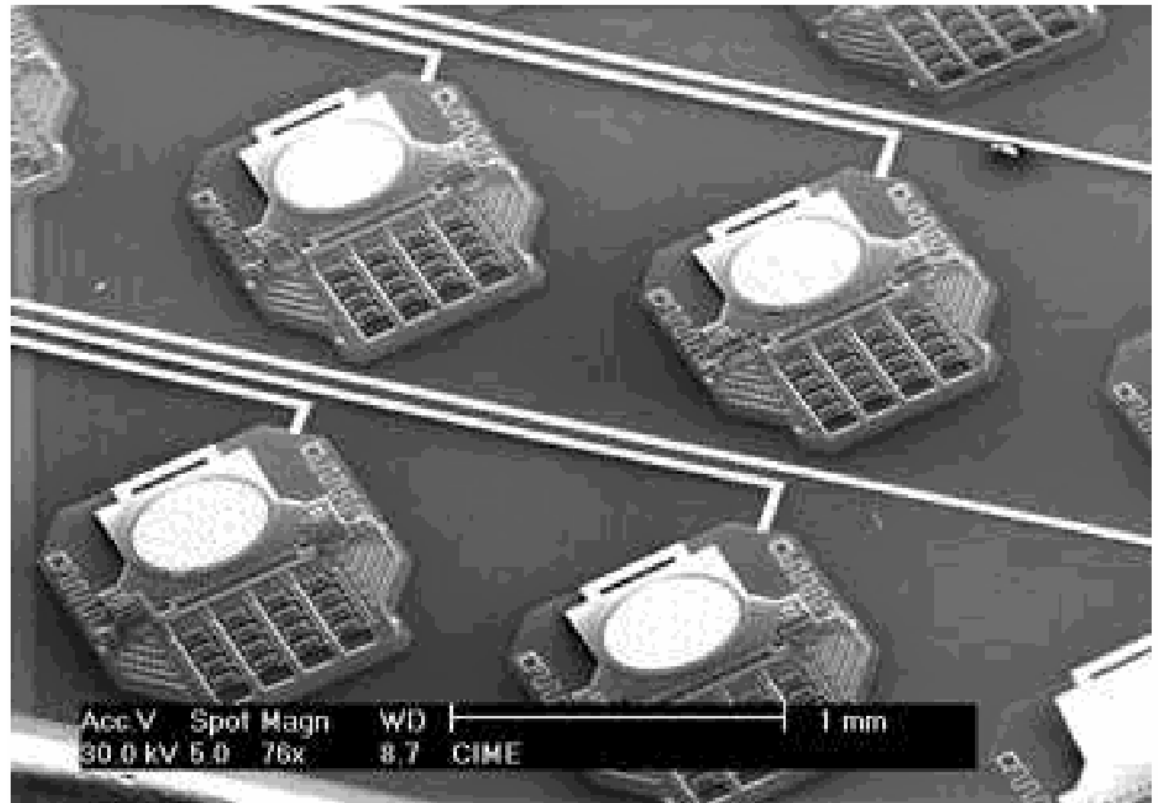
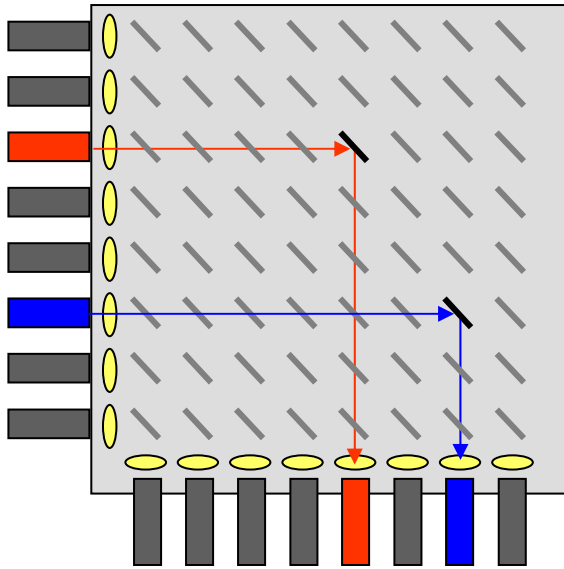
Bar State



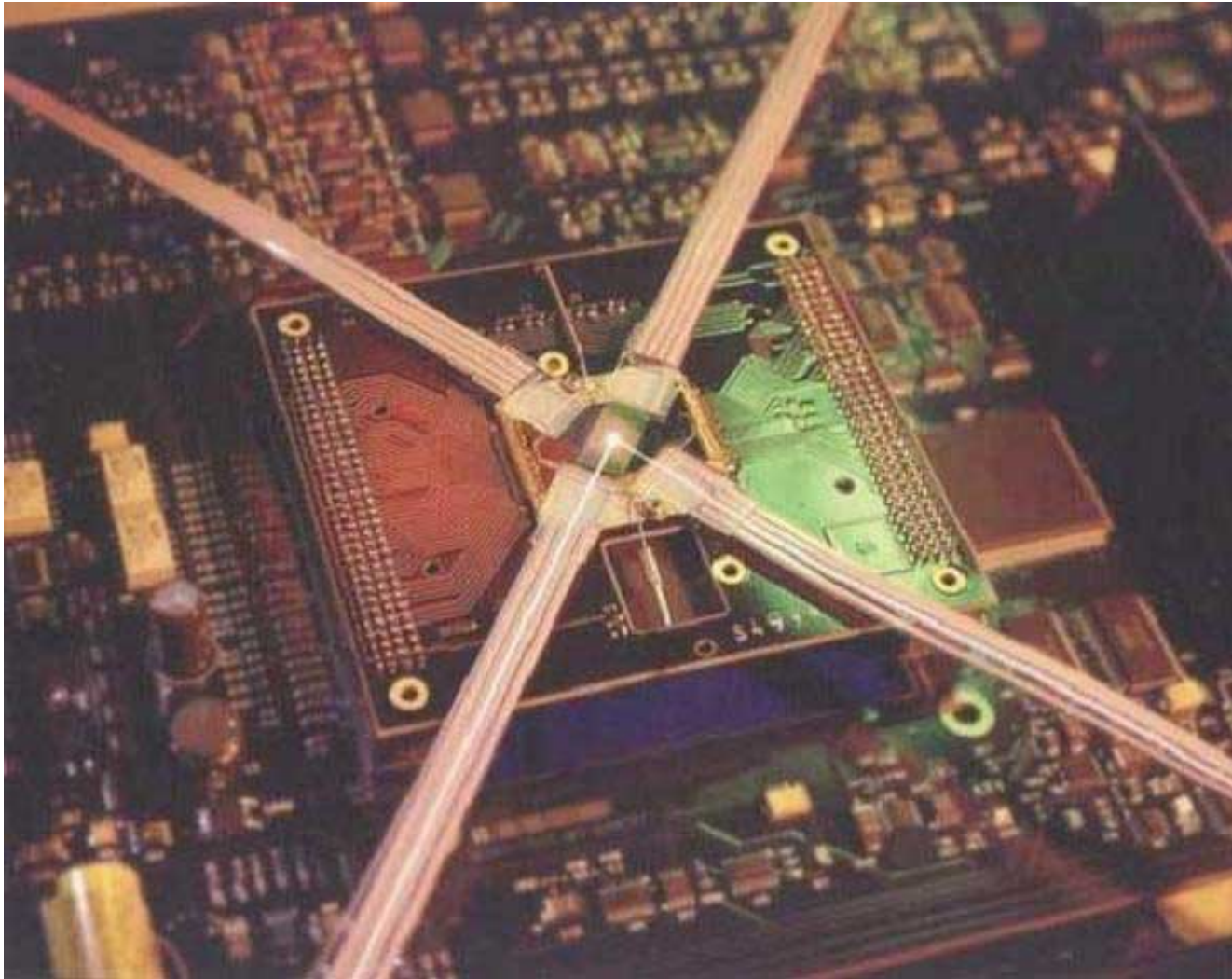
Optical Switch



NxN Optical Link



Agilent Bubble Switch



Segmented Mirrors

- Space Optical Telecommunication
 - Reliable, Small in size, Light in weight, & Easy to fabricate
- Air Turbulence causes optical aberrations
- Quick response time, therefore able correct optical aberrations

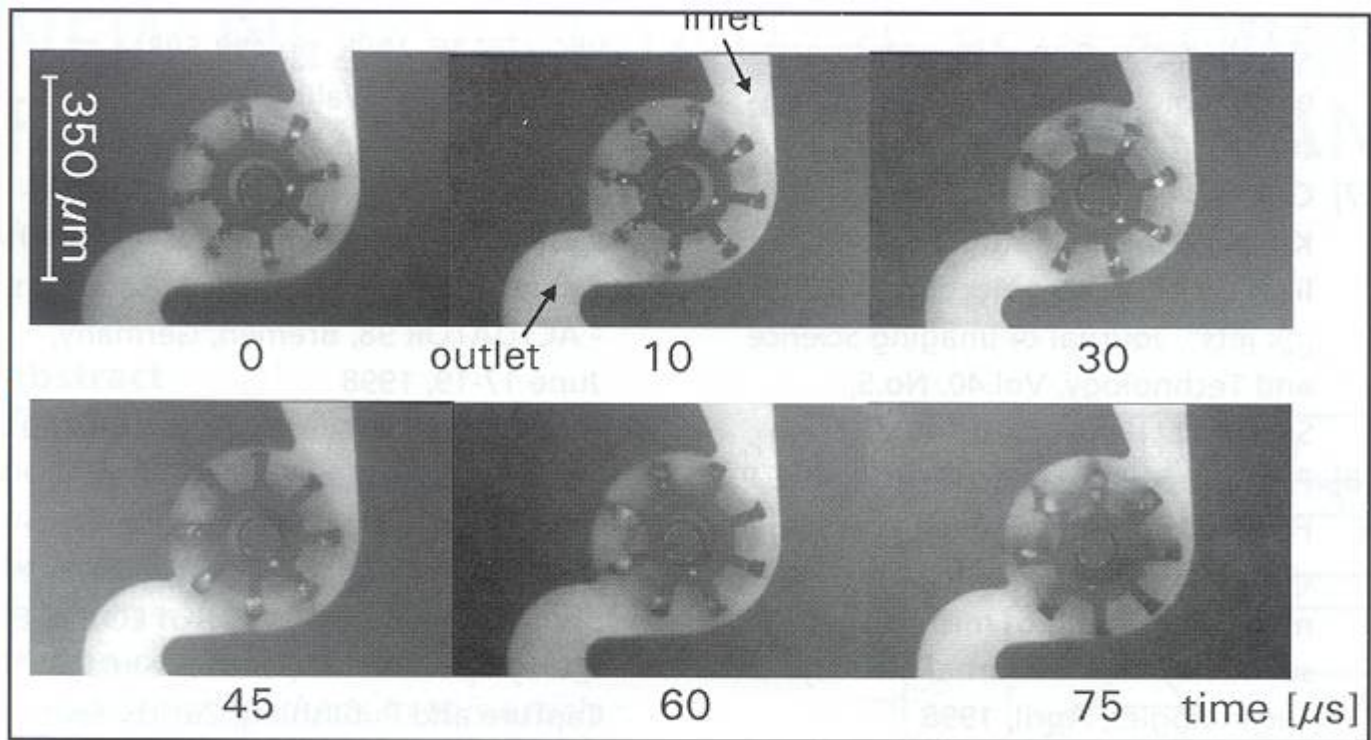


Fig.3: Visualization of the stationary rotation of a pneumatic driven microturbine.

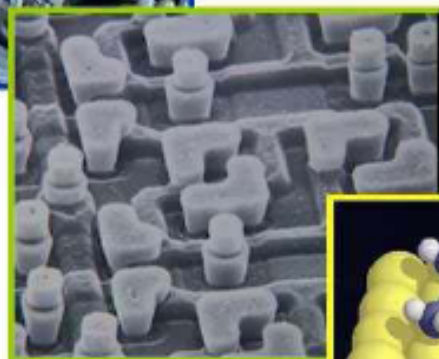
結語

Macro – Micro - Nano



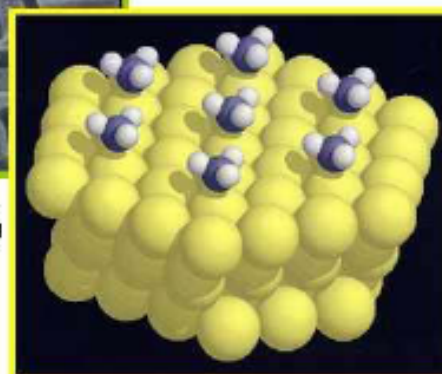
Macro or Conventional
Machines

(m - mm)



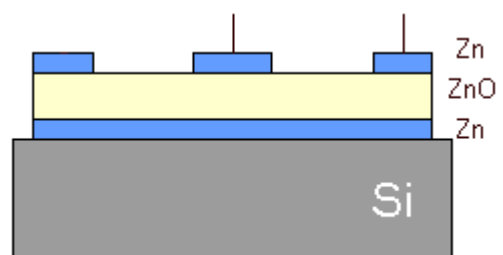
Micromachines

(0.1 mm - 0.1 μ m)



Nanosystems

(100- 1 nm)



>

